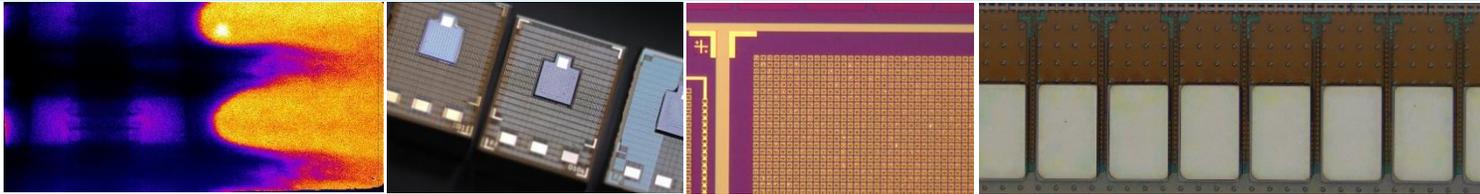
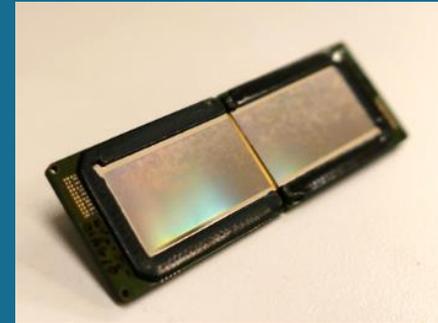




Sandia  
National  
Laboratories

# Ultrafast Imaging with the UXI Family of Hybrid CMOS Detectors



Quinn Looker

Sandia National Laboratories  
Albuquerque, NM

International Forum on Detectors for Photon Science (IFDEPS)  
Brookhaven National Laboratory  
March 17-20, 2024



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Nuclear Security Administration under  
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**SAND2024-03049PE**

# The UXI Program is a Multi-Organizational Effort



**Sandia  
National  
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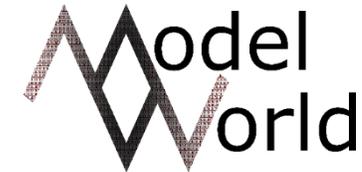


Marcos Sanchez  
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Matthew Dayton  
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Arthur Carpenter  
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Brandon Morioka

Brad Golick  
Robin Benedetti  
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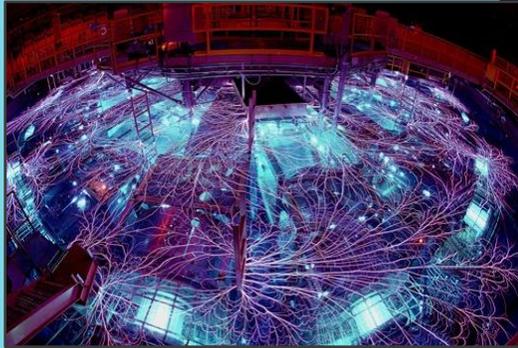
**NHanced Semiconductors, Inc.**



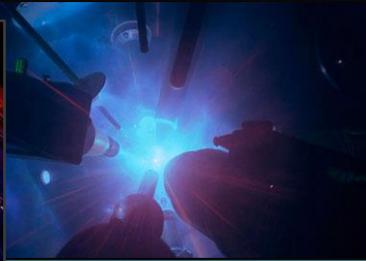
# Sandia's Hybrid CMOS Detectors were Developed for Inertial Confinement Fusion and High Energy Density Physics Applications



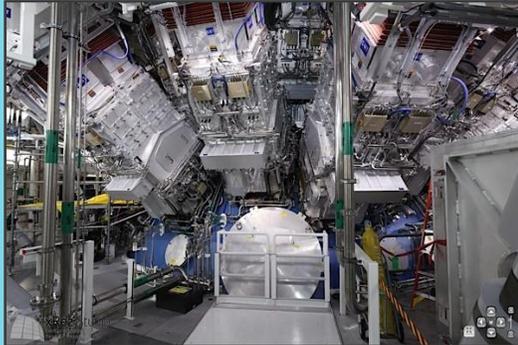
## National Inertial Confinement Fusion Facilities



Sandia Z Machine



OMEGA LLE



Livermore NIF



CEA LMJ

- High Intensity (~MJ x-rays,  $10^{17}$  neutrons in ~ns)
- Low Shot Rate (<5 shots/day)

## Light & Particle Sources



SLAC LCLS



Sandia ZBL



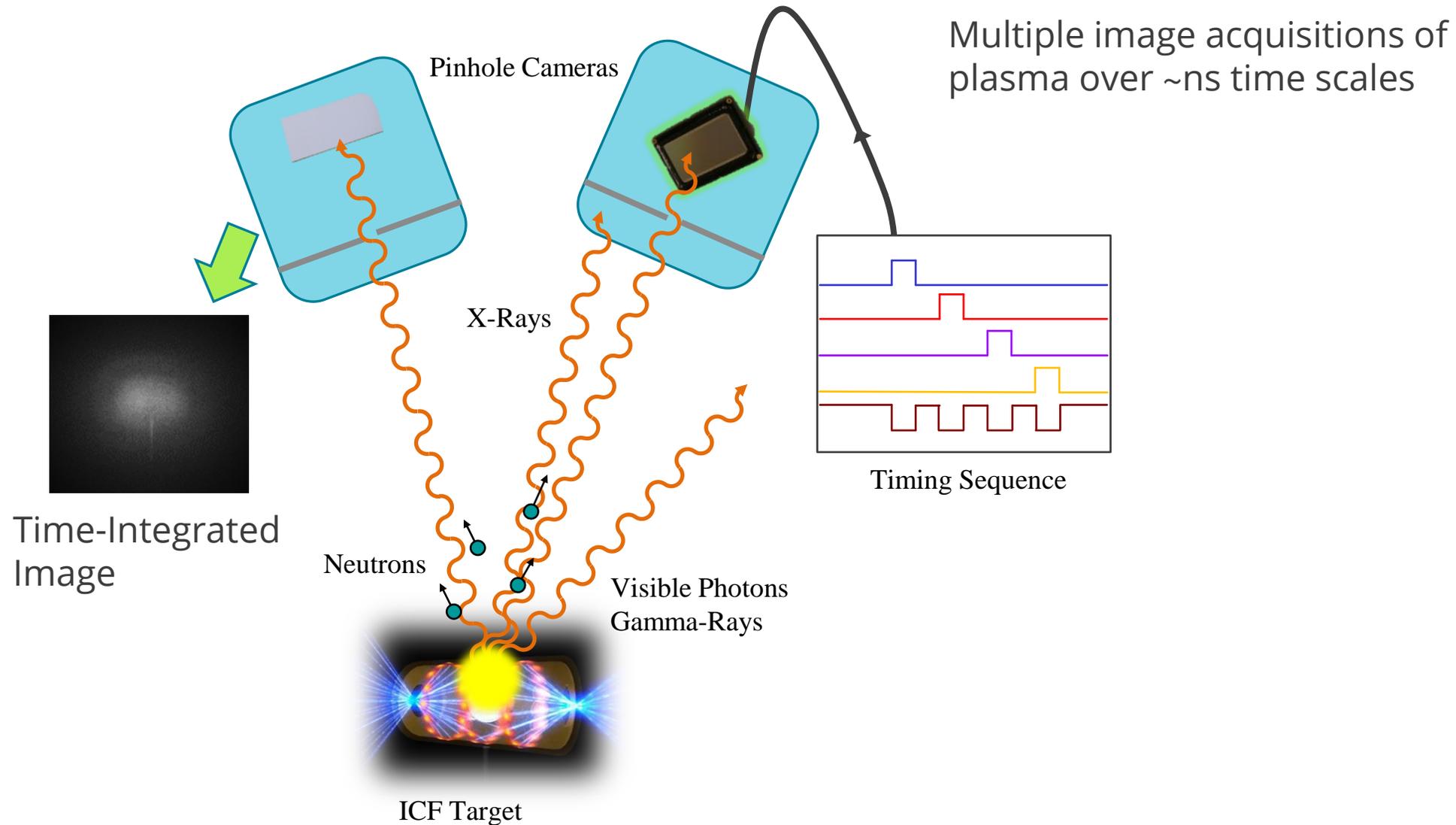
ANL APS



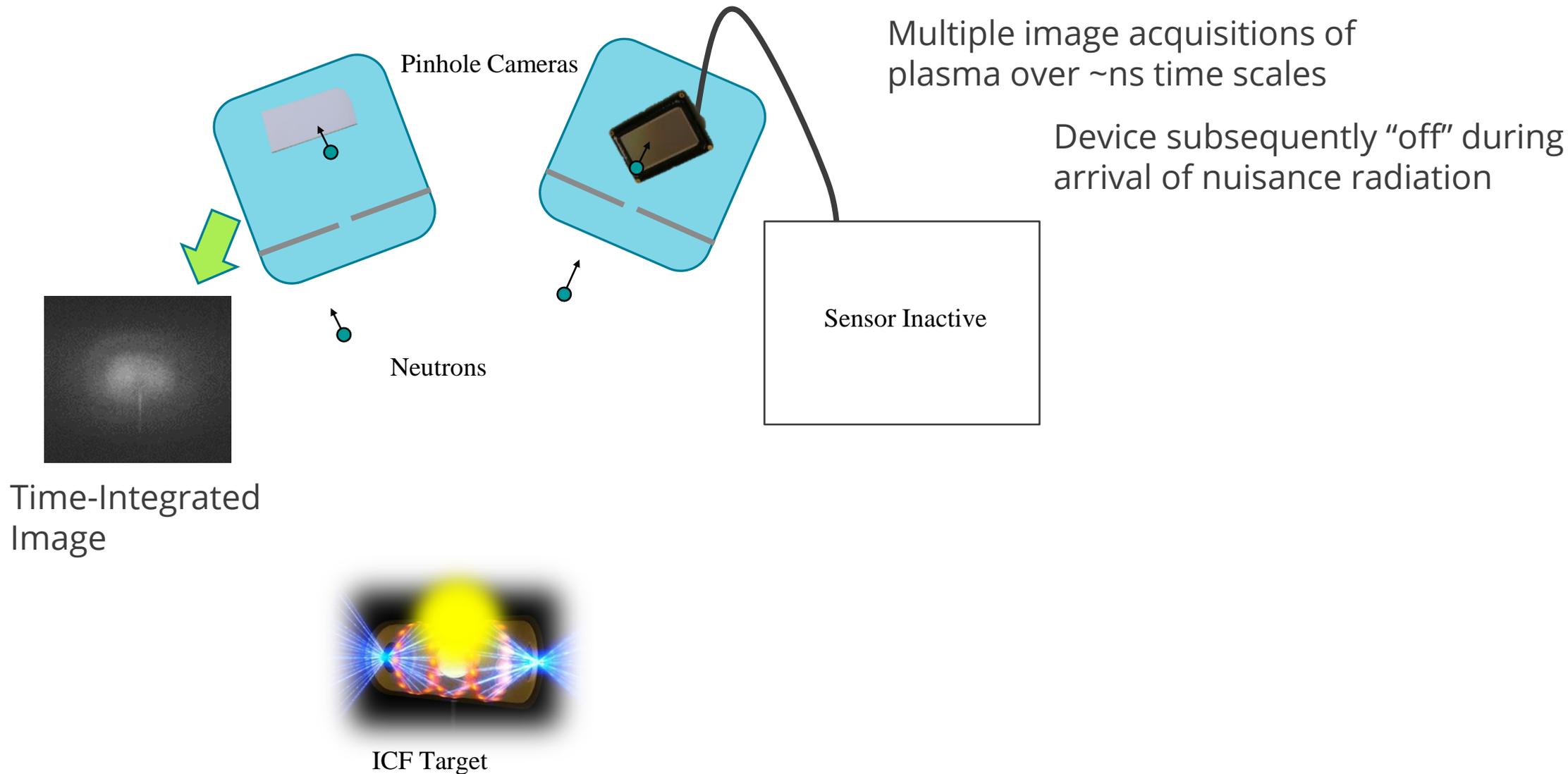
LLNL JLF

- Early work adapting to light sources
- Higher rep rate, lower intensity

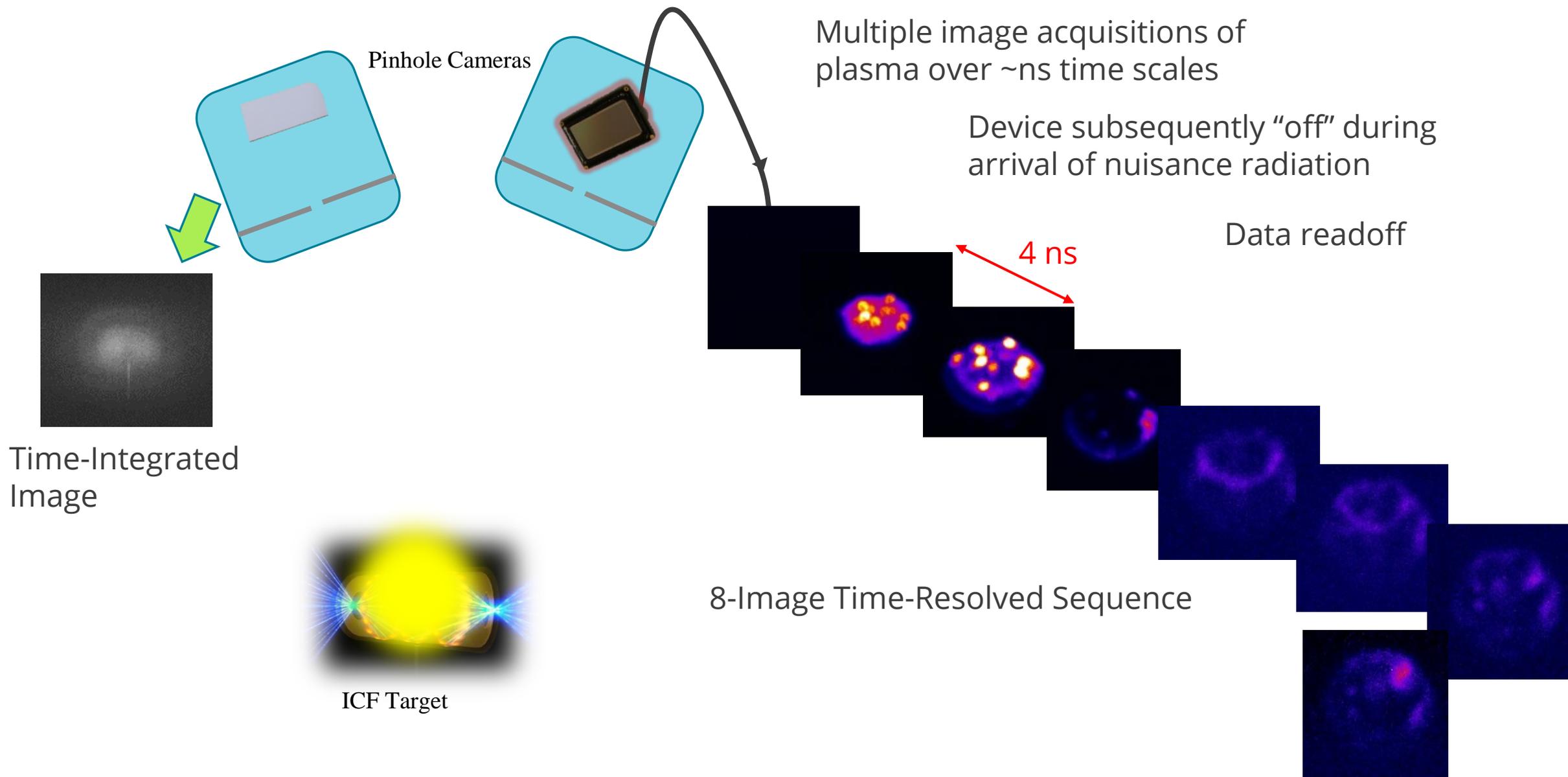
# Burst-Mode Imaging Used for Rapidly Evolving Plasmas



# Burst-Mode Imaging Used for Rapidly Evolving Plasmas

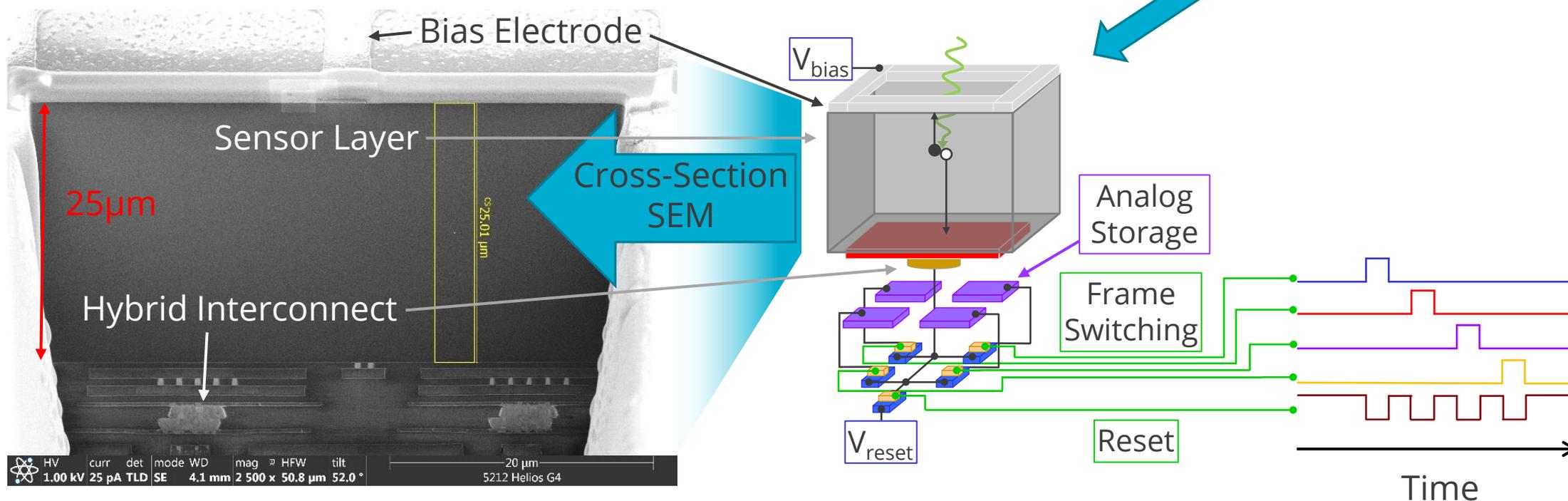
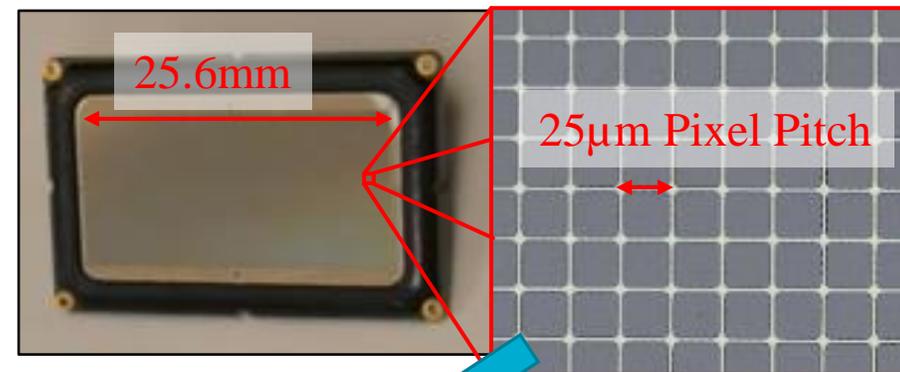


# Burst-Mode Imaging Used for Rapidly Evolving Plasmas



# Hybrid CMOS Detectors Enable Multiple, Time-Resolved Images Along a Single Line-Of-Sight

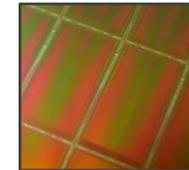
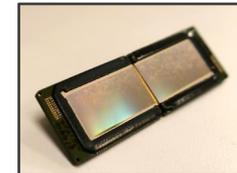
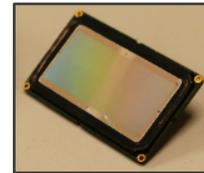
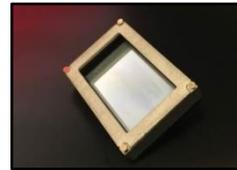
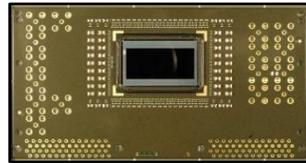
- Direct detection in semiconductor sensor
- High Soft X-ray Quantum Efficiency (50% for 6 keV)
- 100% fill factor within 3.2 cm<sup>2</sup> area
- Multiple frames on identical line-of-sight
- Digital image readout



# The Sandia hCMOS Family has Two Branches

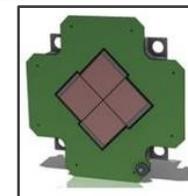
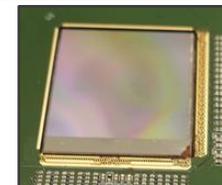


	Retired		Deployed	Prototype	In Production
	Furi	Hippogriff	Icarus V1/V2	Daedalus V1/V2	Tantalus
Min. Integration time	~1.5 ns	~2 ns	~1.5 ns	~1.0 ns	~0.5 ns
Frames	2	2 <sup>a</sup>	4 <sup>b</sup>	3 <sup>a,b</sup>	4 <sup>a,c</sup>
Pixels	448 × 1024	448 × 1024	512 × 1024	512 × 1024	512 × 1024
Capacitor Full Well	1.5 million e <sup>-</sup>	1.5 million e <sup>-</sup>	0.7 million e <sup>-</sup>	1.5 million e <sup>-</sup>	0.5 million e <sup>-</sup>



- <sup>a</sup> Row interlacing option for 2x, 4x, or more frames  
<sup>b</sup> Left/right half independent timing  
<sup>c</sup> Quadrant independent timing  
<sup>d</sup> Doubled when CDS inactive

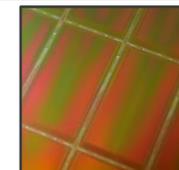
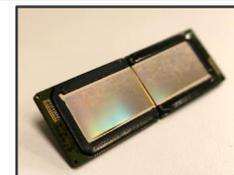
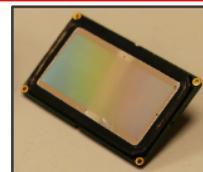
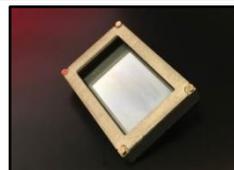
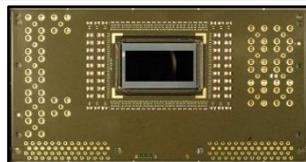
	Retired	Prototype	In Production
	Proteus	Kraken V1	Kraken V2
Min. Integration time	50 ns	50 ns	50 ns
Frames	4 <sup>d</sup>	4 <sup>d</sup>	8
Pixels	256 × 768	800 × 800	800 × 800
Capacitor Full Well	0.4 million e <sup>-</sup>	0.4 million e <sup>-</sup>	0.4 million e <sup>-</sup>



# The Sandia UXI Family Comprises Nanosecond Gated Sensors



	Retired		Deployed	Prototype	In Production
	Furi	Hippogriff	Icarus V1/V2	Daedalus V1/V2	Tantalus
Year	FY14	FY15	FY16-18	FY18-23	FY24
Min. Integration time	~1.5 ns	~2 ns	~1.5 ns	~1.0 ns	~0.5 ns
Frames	2 (full resolution)	2 (full resolution) 4 or 8 (Row interlaced)	4 (full resolution) 8 (L/R interlaced)	3 (full resolution) 6+ (Row/L/R interlaced)	4 (full resolution) 16+ (Row/quad. interlaced)
Tiling Option	No	No	No	One Side	No
CMOS Process	350 nm (SNL)	350 nm (SNL)	350 nm (SNL)	350 nm (SNL)	130 nm (Tower Jazz)
Pixels	448 × 1024	448 × 1024	512 × 1024	512 × 1024	512 × 1024
Pixel Size	25 μm × 25 μm	25 μm × 25 μm	25 μm × 25 μm	25 μm × 25 μm	25 μm × 25 μm
Capacitor Full Well	1.5 million e <sup>-</sup>	1.5 million e <sup>-</sup>	0.7 million e <sup>-</sup>	1.5 million e <sup>-</sup>	0.5 million e <sup>-</sup>



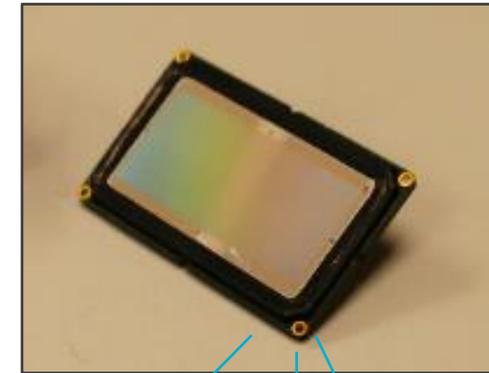
# Icarus is the First Widely Deployed Detector of the SNL hCMOS Family

- First true half Megapixel array of the line
- 4 frames per pixel
- Higher gain optimized for smaller signals
- Small package constructed using standard techniques

	Icarus
<b>Tech. Node</b>	SNL 350nm
<b># Pixels</b>	1024 x 512
<b>Pixel Size</b>	25 $\mu$ m x 25 $\mu$ m
<b># Frames</b>	4 <sup>a</sup>
<b>Full well</b>	700ke <sup>-</sup>
<b>Min. gate time</b>	~1.5ns
<b>Abutment</b>	No

<sup>a</sup> 8 frames possible when using independent sensor half timing

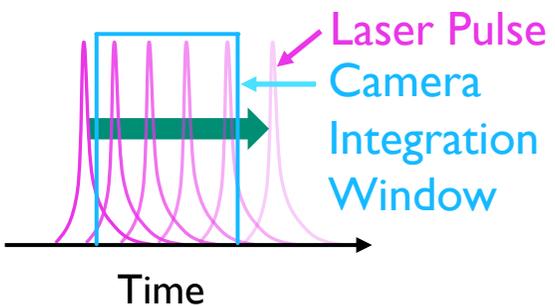
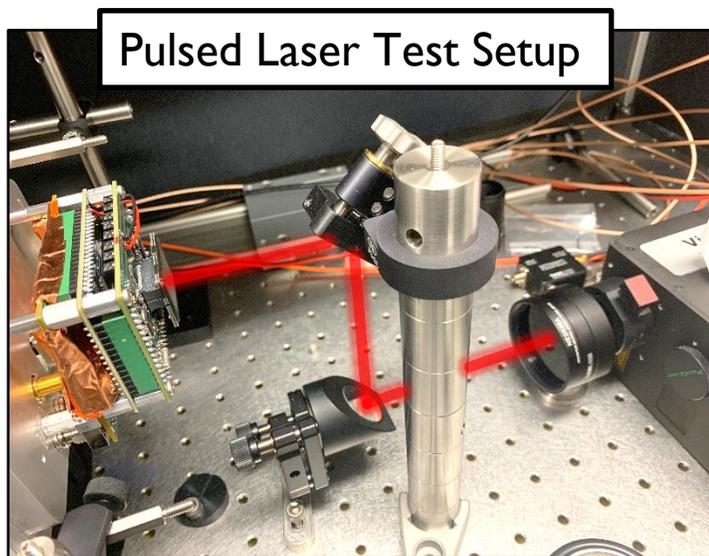
Icarus Detector Module



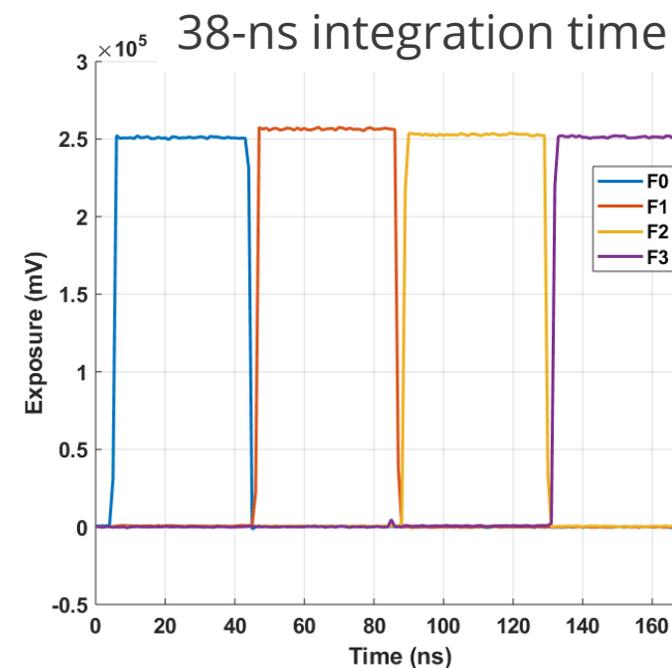
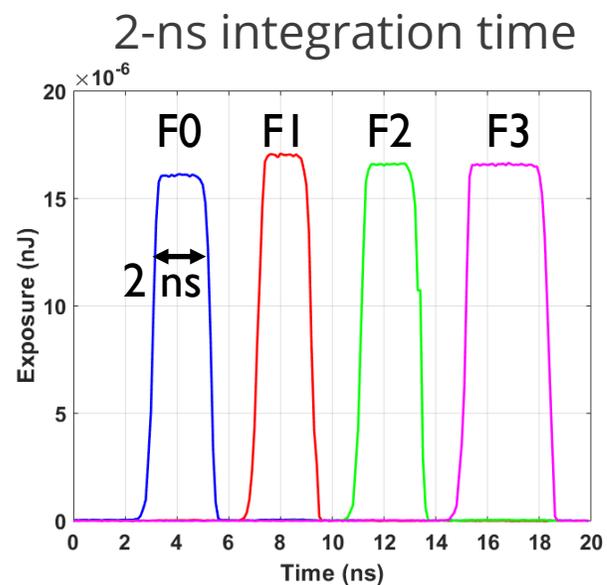
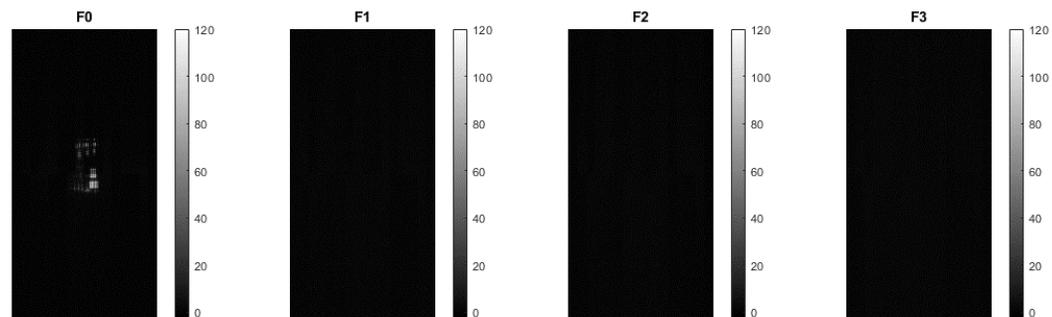
Supporting Electronics Variants

# Routine Optical Characterization Demonstrates Multi-Frame Integration Capability

- Direct pulsed laser illumination of sensor
- Vary relative delay of camera and laser

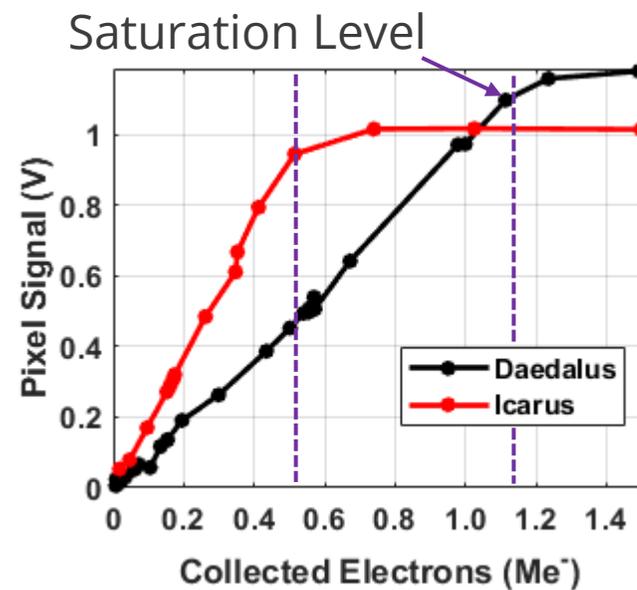
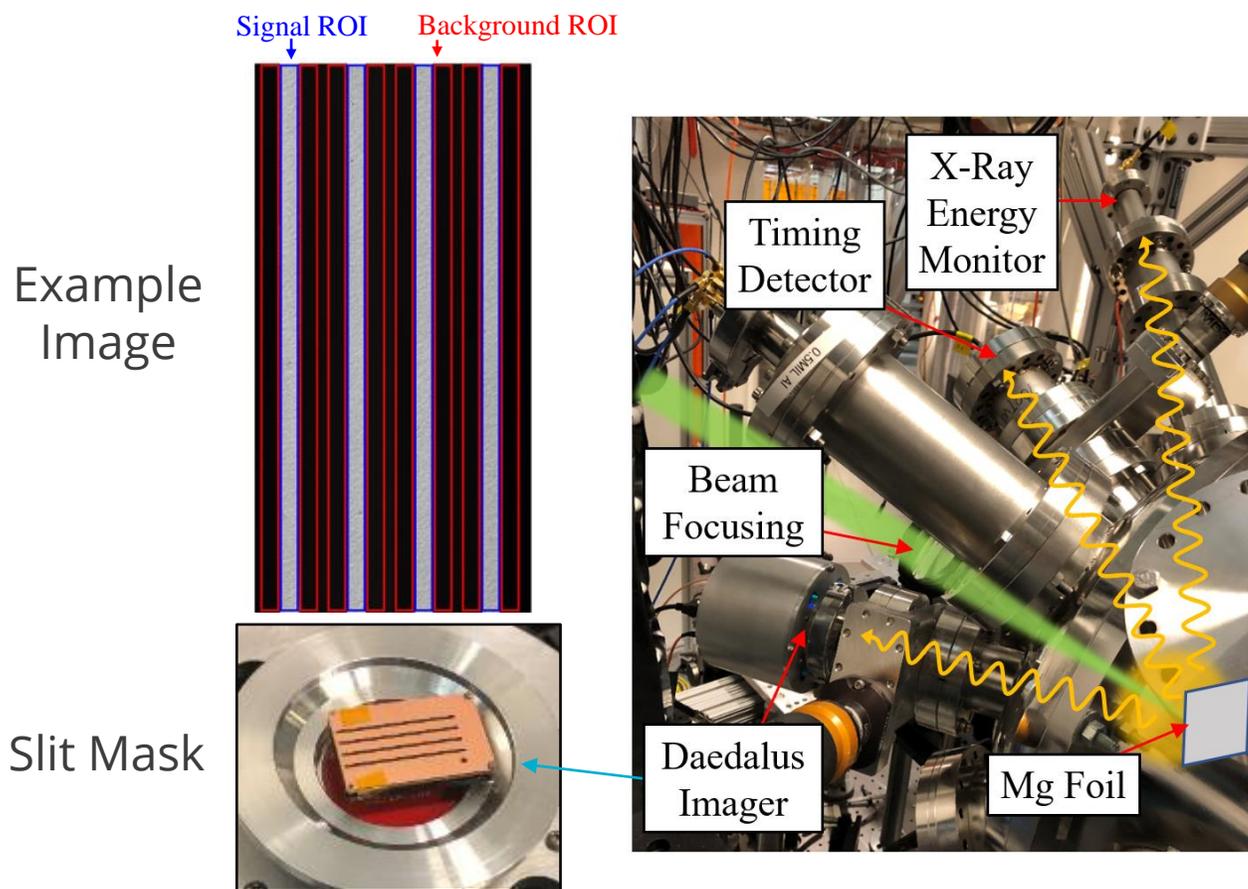


Example Image Set



# Pulsed X-Ray Characterization Demonstrates Linearity and Saturation Behavior

- Laser-induced plasma x-ray source  $\sim 1\text{ns}$  duration
- Intensity measured by x-ray photodiodes
- Imager response in linear region and saturation



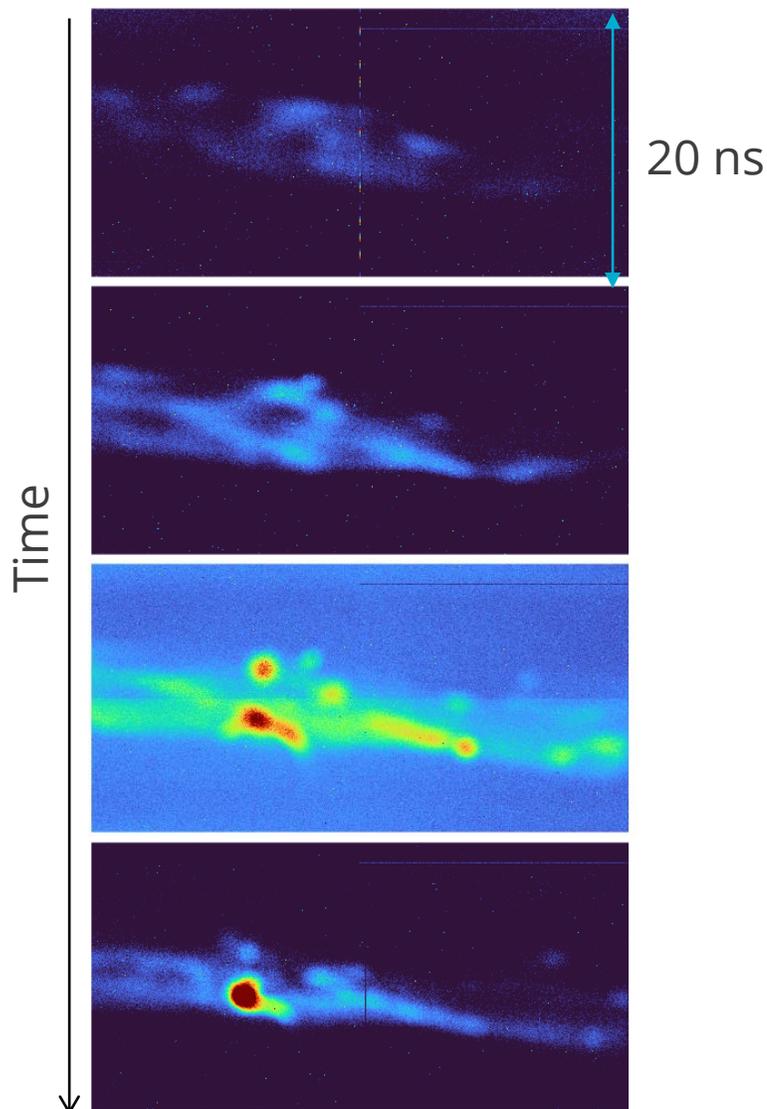
Looker et al., *RSI* 91 043502 (2020)

Looker et al., *RSI* 94 113505 (2023)

# Icarus Enables Time-Resolved Imaging of Hot Plasmas



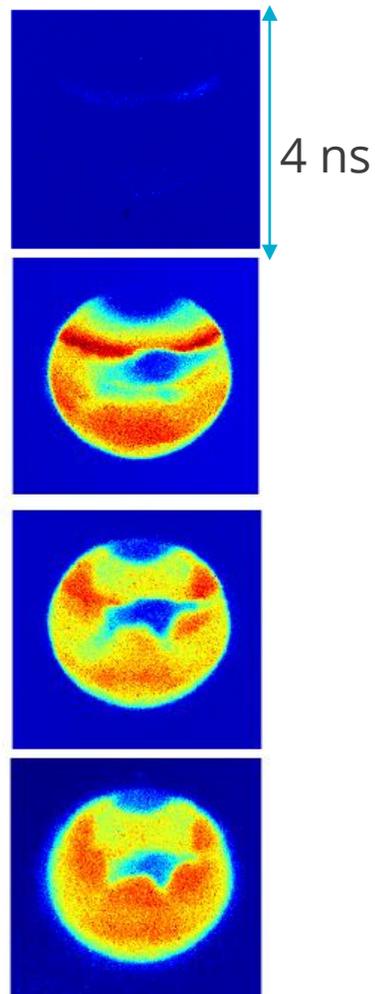
Evolution of magnetic reconnection layer on Z



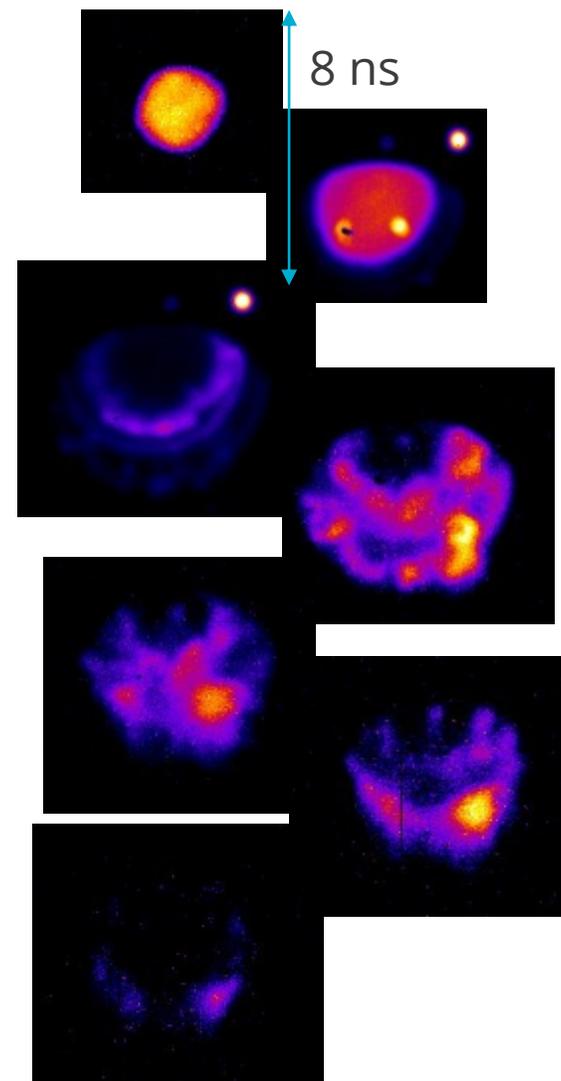
R. Datta et al., *PRL* in review

Laser Entrance Window of MagLIF Target

Gated LEH Images on NIF



H. Chen et al., *RSI*. 87 11e203 (2016)

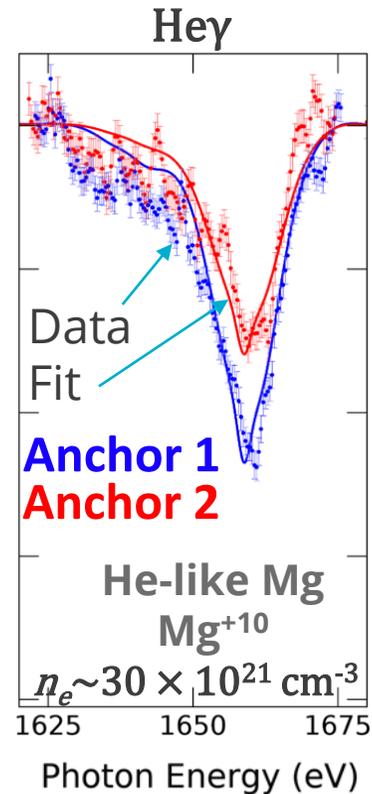
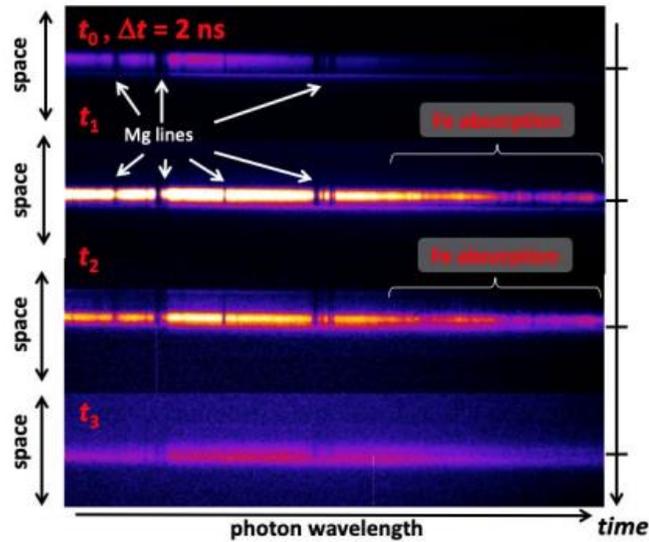


# Icarus Enables Time-Resolved Spectroscopy



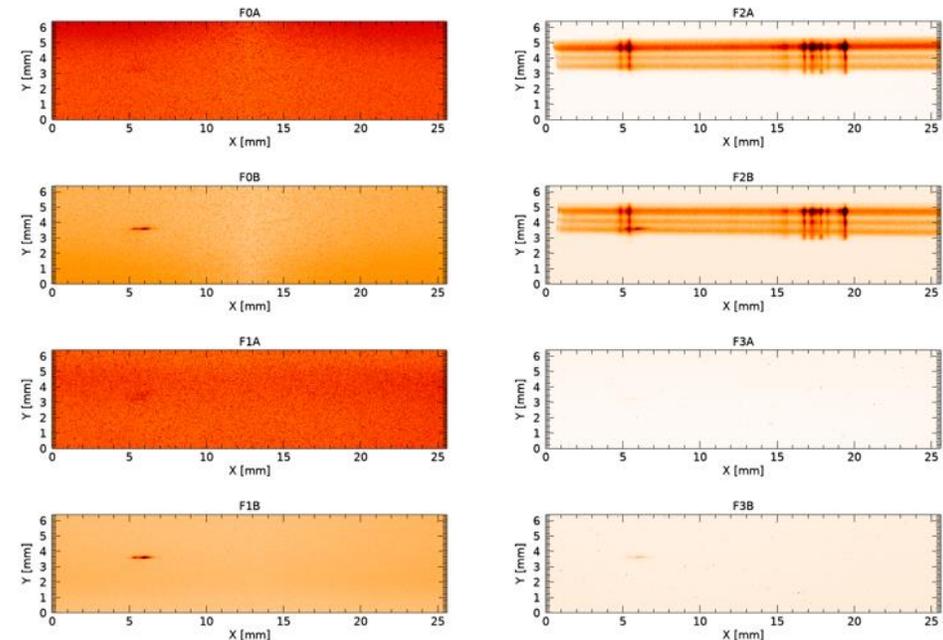
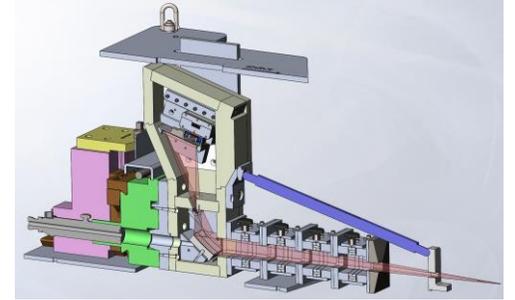
## Opacity Platform

Adding time resolution to quantitative opacity measurements on Z and NIF



## MONSSTR

Time-resolved spectrometer for hot plasmas on Z

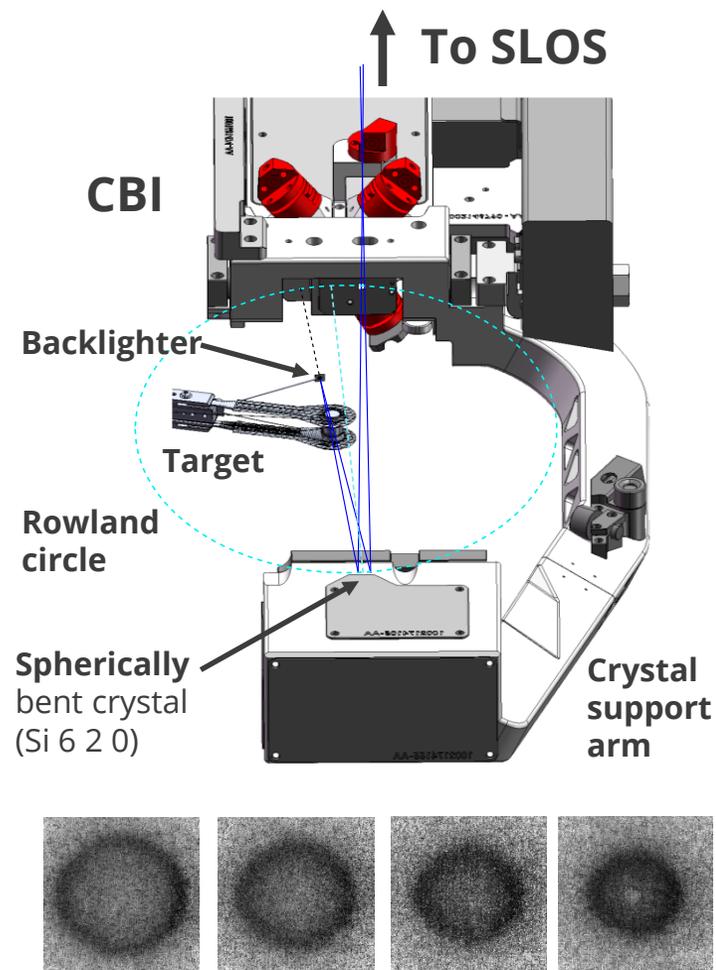


# Icarus Enables Multi-Frame Gated Backlighting



## CBI-SLOS on NIF

Time-resolved mix measurement in imploding capsules

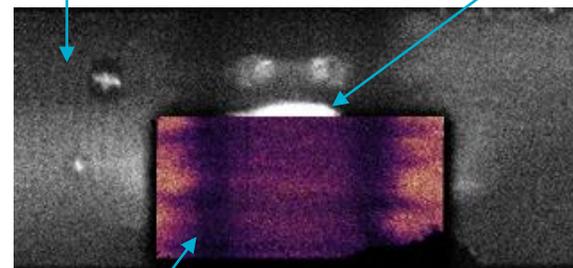


## Gated Backlighting on Z

A single gated image avoids target self-emission...

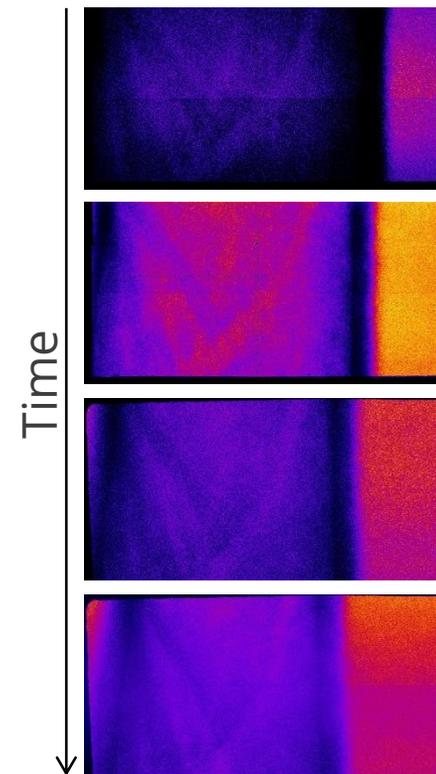
Time-Integrated Image

Target Self-Emission



Gated Image

And newly developed multi-frame backlighting provides multiple measurements *on the same shot*.

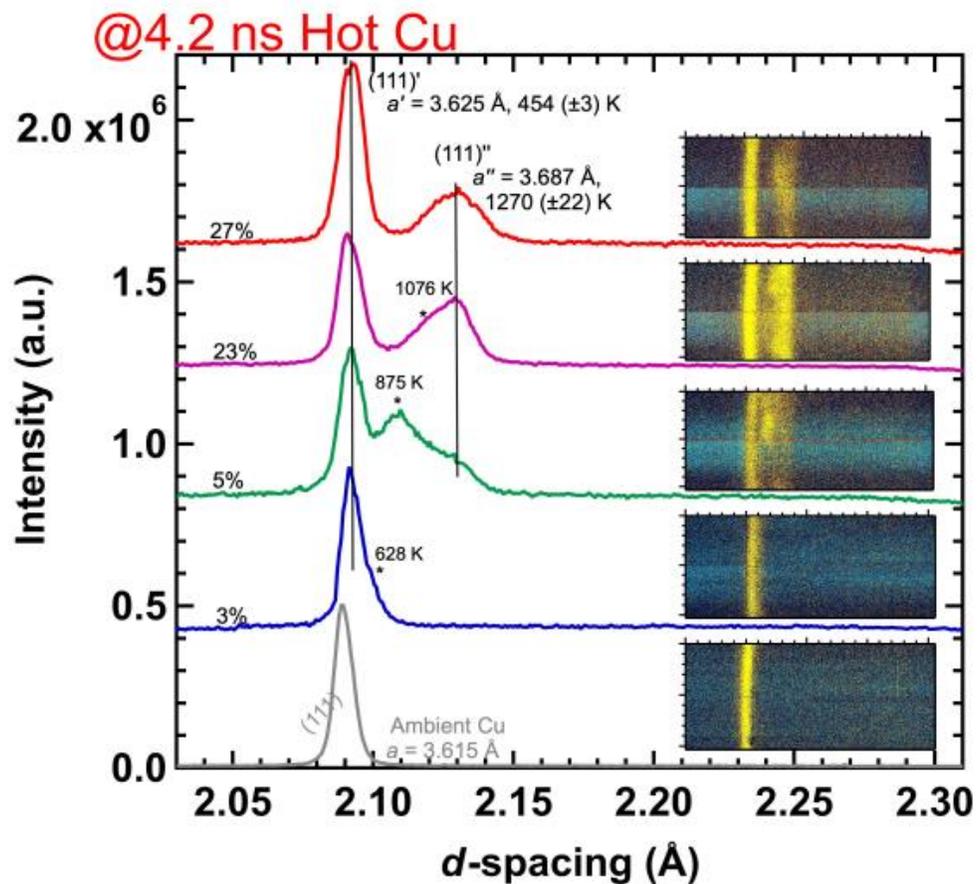


# Initial Demonstration of Icarus Performance at Light Sources

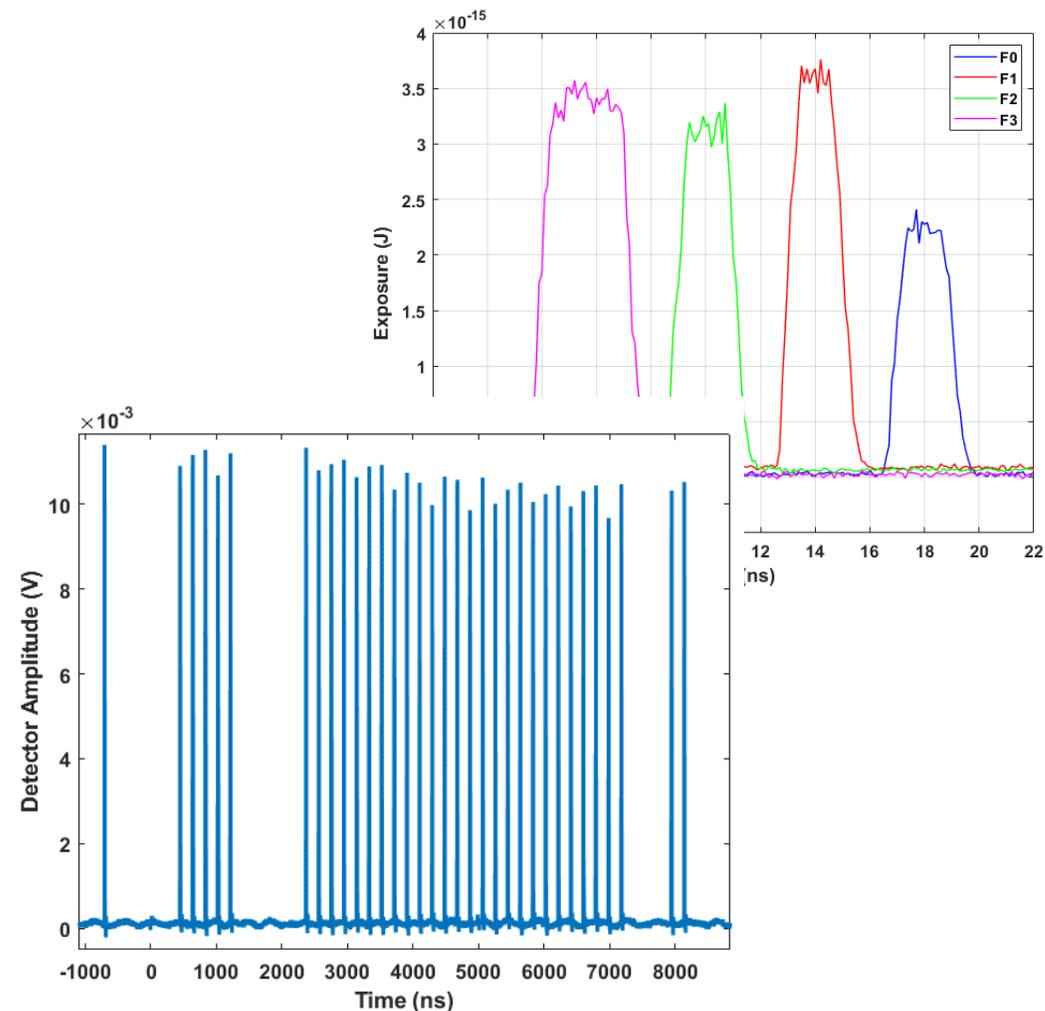


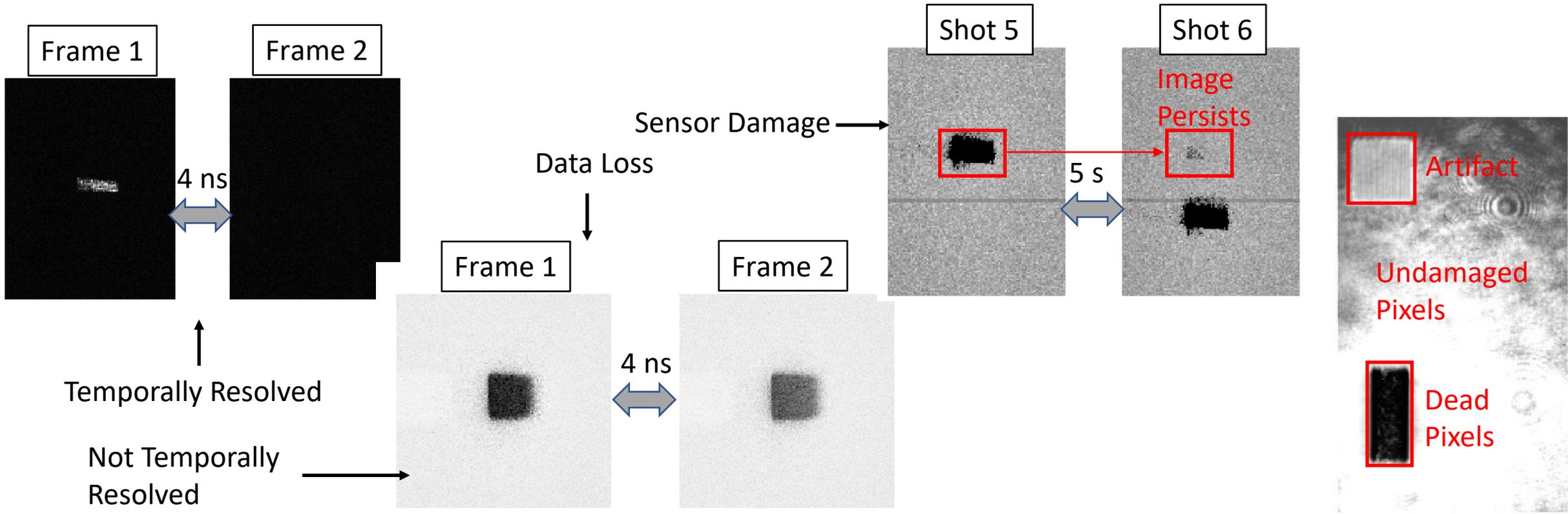
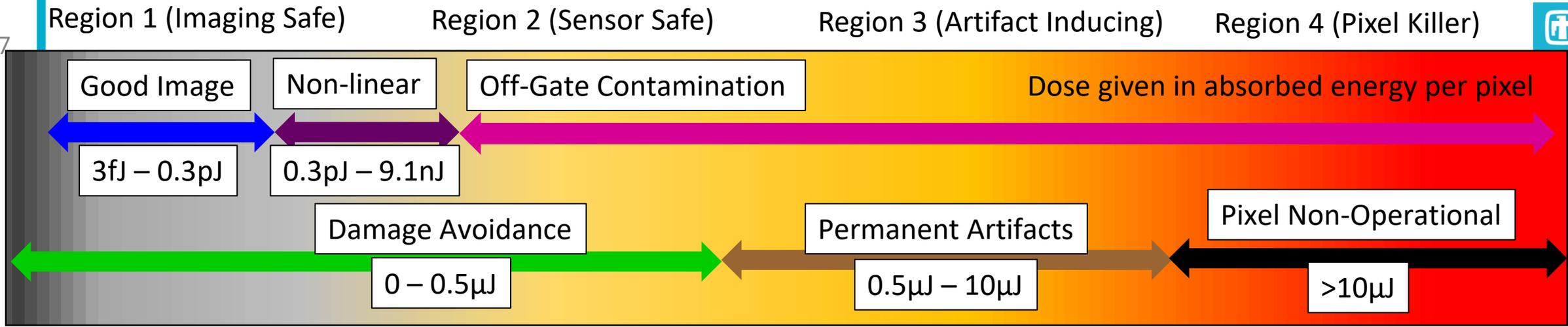
Time-resolved diffraction of dynamically heated Cu at LCLS

Demo with TX Products WaveGate at PETRA III



P. Hart et al., *Proc. SPIE* 110380Q (2019)

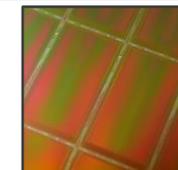
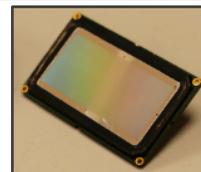
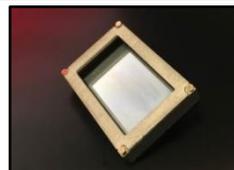
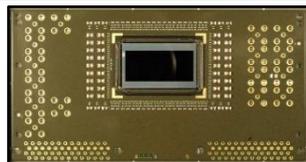




# The Sandia UXI Family Comprises Nanosecond Gated Sensors



	Retired		Deployed	Prototype	In Production
	Furi	Hippogriff	Icarus V1/V2	Daedalus V1/V2	Tantalus
Year	FY14	FY15	FY16-18	FY18-23	FY24
Min. Integration time	~1.5 ns	~2 ns	~1.5 ns	~1.0 ns	~0.5 ns
Frames	2 (full resolution)	2 (full resolution) 4 or 8 (Row interlaced)	4 (full resolution) 8 (L/R interlaced)	3 (full resolution) 6+ (Row/L/R interlaced)	4 (full resolution) 16+ (Row/quad. interlaced)
Tiling Option	No	No	No	One Side	No
CMOS Process	350 nm (SNL)	350 nm (SNL)	350 nm (SNL)	350 nm (SNL)	130 nm (Tower Jazz)
Pixels	448 × 1024	448 × 1024	512 × 1024	512 × 1024	512 × 1024
Pixel Size	25 μm × 25 μm	25 μm × 25 μm	25 μm × 25 μm	25 μm × 25 μm	25 μm × 25 μm
Capacitor Full Well	1.5 million e <sup>-</sup>	1.5 million e <sup>-</sup>	0.7 million e <sup>-</sup>	1.5 million e <sup>-</sup>	0.5 million e <sup>-</sup>



# Daedalus is the Newly Completed Addition to the UXI Family



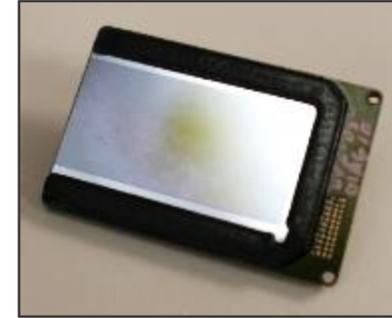
- Highly similar to Icarus in performance and form factor
- Shorter minimum integration time
- Higher full well
- New timing modes added
- Two-detector abutment
- Temperature sensor and corner diode

	Icarus	Daedalus
Tech. Node	SNL 350nm	SNL 350nm
# Pixels	1024 x 512	1024 x 512
Pixel Size	25 $\mu$ m x 25 $\mu$ m	25 $\mu$ m x 25 $\mu$ m
# Frames	4 <sup>a</sup>	3 <sup>a,b</sup>
<b>Full well</b>	<b>700ke<sup>-</sup></b>	<b>1.5Me<sup>-</sup></b>
Min. gate time	~1.5ns	~1.0ns
Abutment	No	1 short side

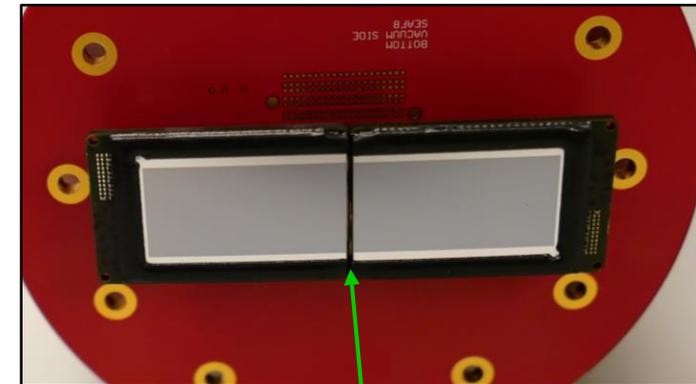
<sup>a</sup> Sensor halves can be independently timed

<sup>b</sup> Row interlacing can multiply number of frames

L. Claus et al., *Proc. SPIE* 107630M (2018)



Combined 12.8mm x 51.2mm Area



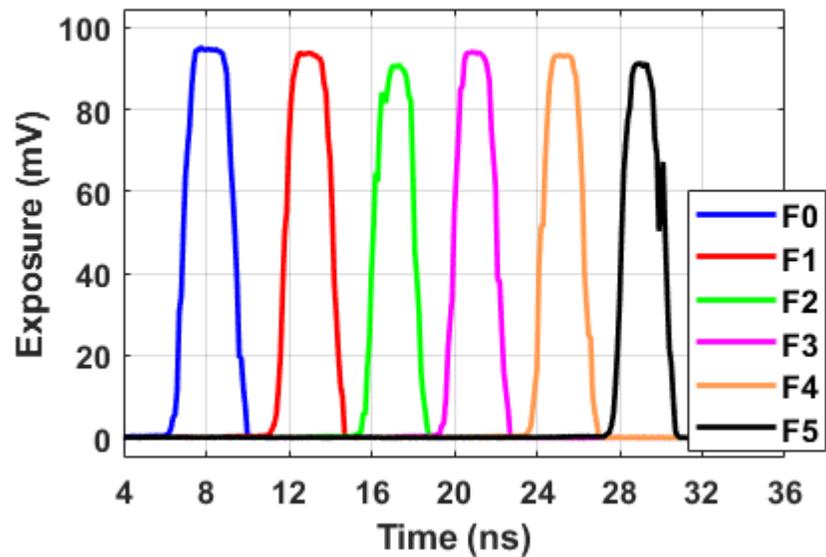
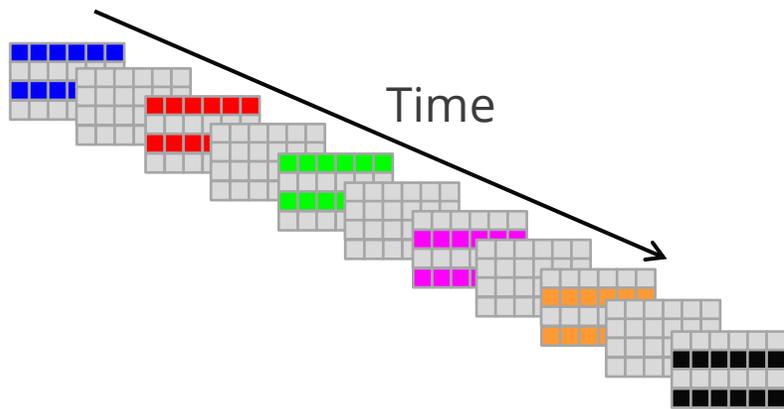
1.25mm Gap

Looker et al., *RSI* 94 113505 (2023)

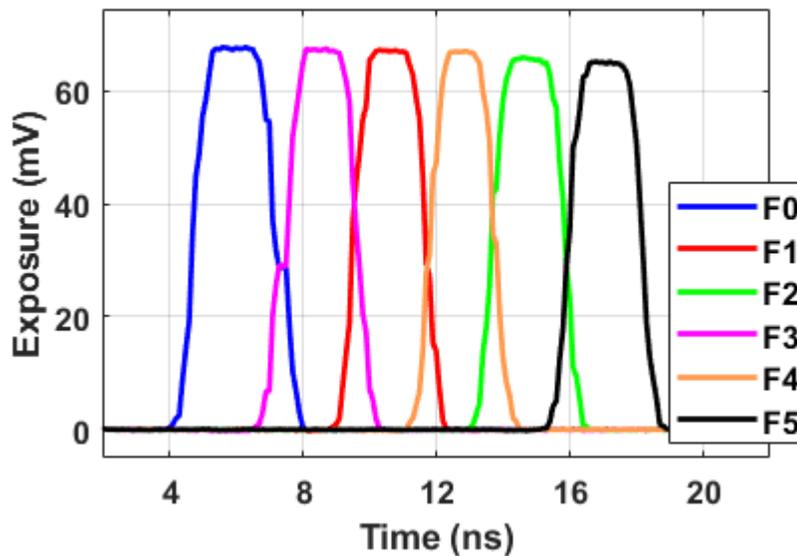
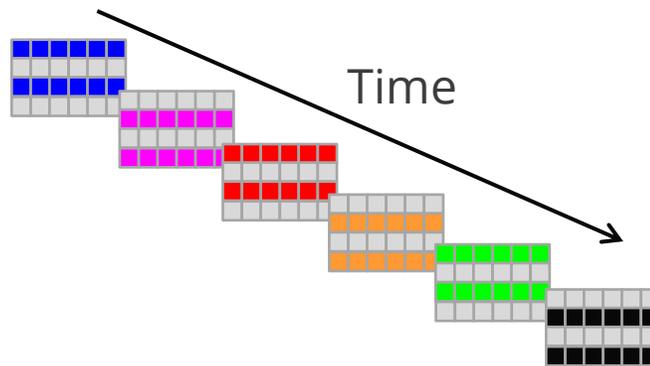
# Daedalus Adds New Timing Flexibility



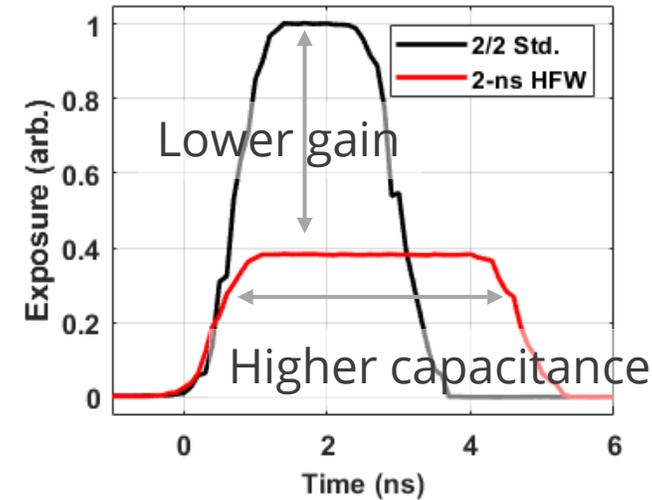
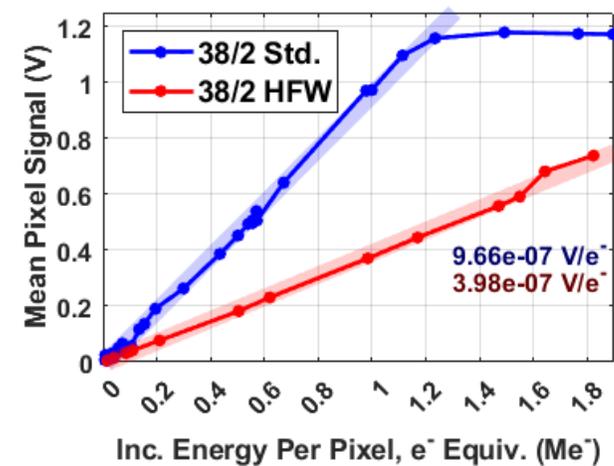
Extend temporal coverage with **row interlacing**



Fill temporal gaps with **zero dead time mode**

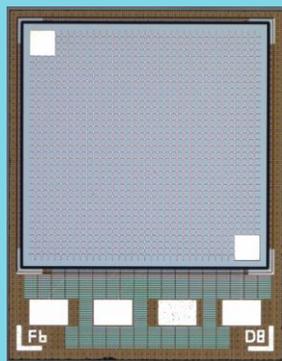
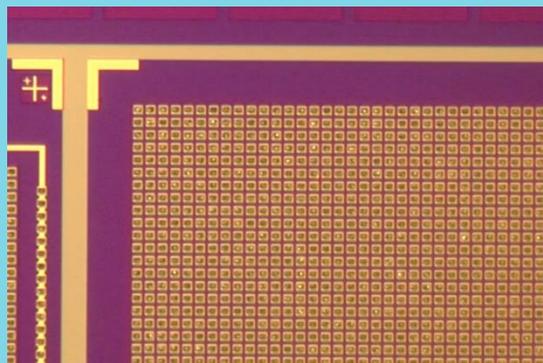


Increase full well with **high full well mode**



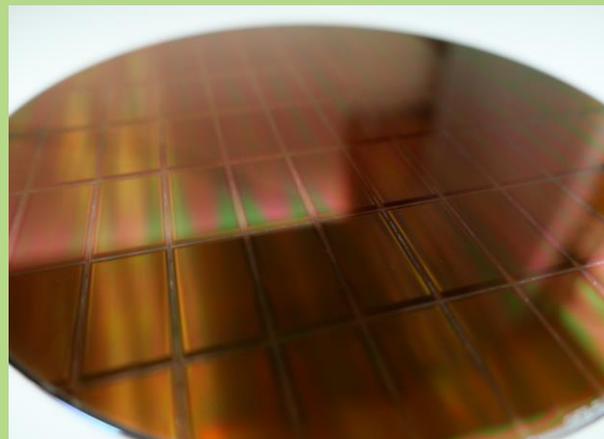
## Sensor development

- Faster charge collection
- Higher atomic number



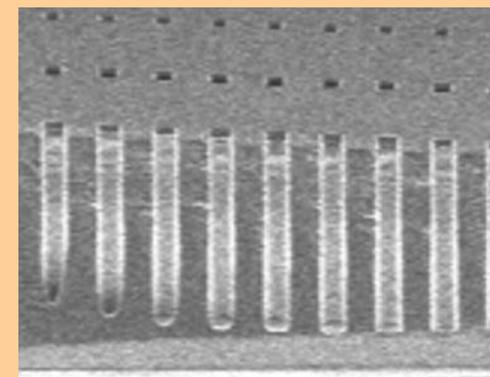
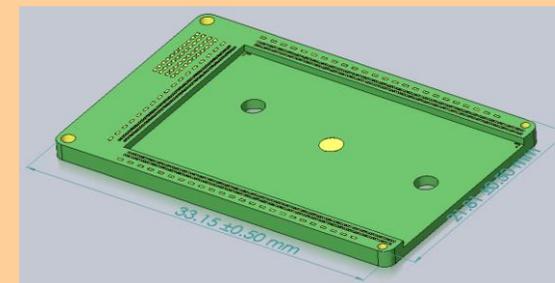
## ROIC development

- Faster gate times
- Increased number of frames
- Smaller nodes
- Commercial foundries



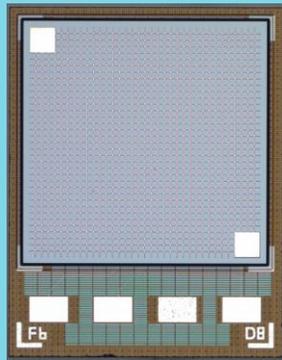
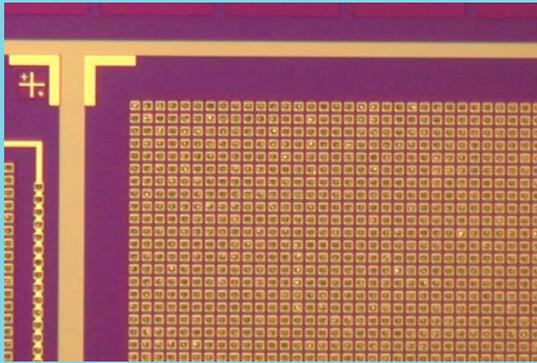
## Package development

- Improved PCB Design
- Through Si Vias
- Thermal Management



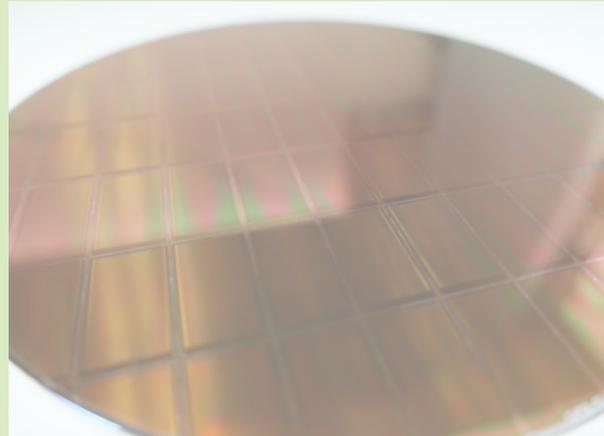
## Sensor development

- Faster charge collection
- Higher atomic number



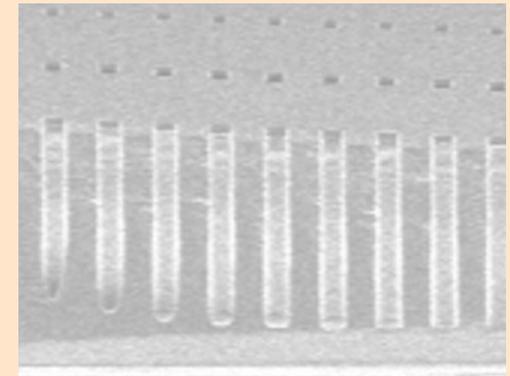
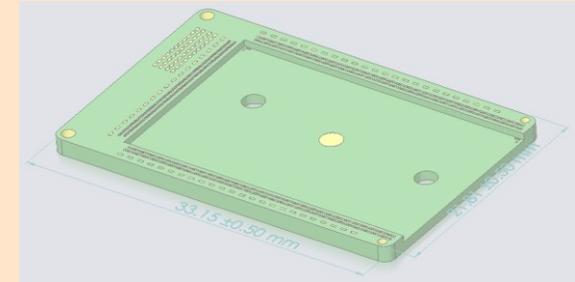
## ROIC development

- Faster gate times
- Increased number of frames
- Smaller nodes
- Commercial foundries



## Package development

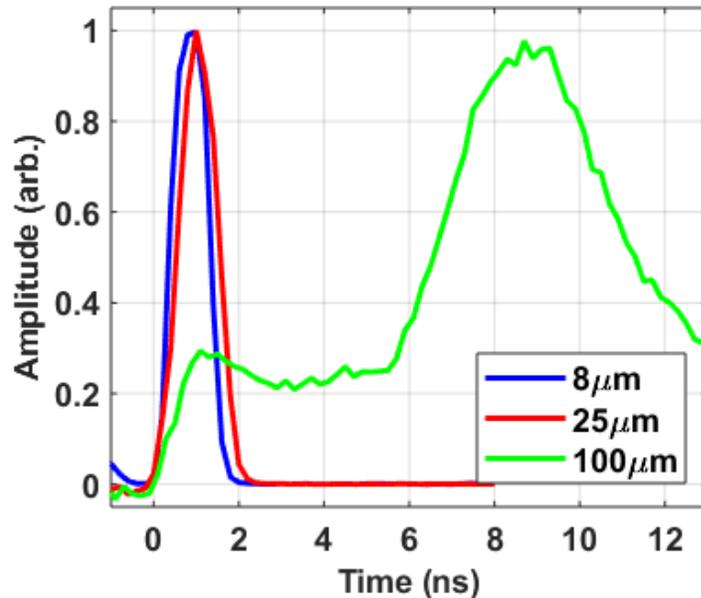
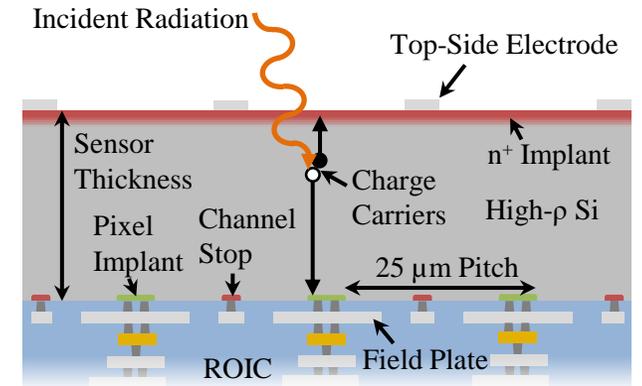
- Improved PCB Design
- Through Si Vias
- Thermal Management



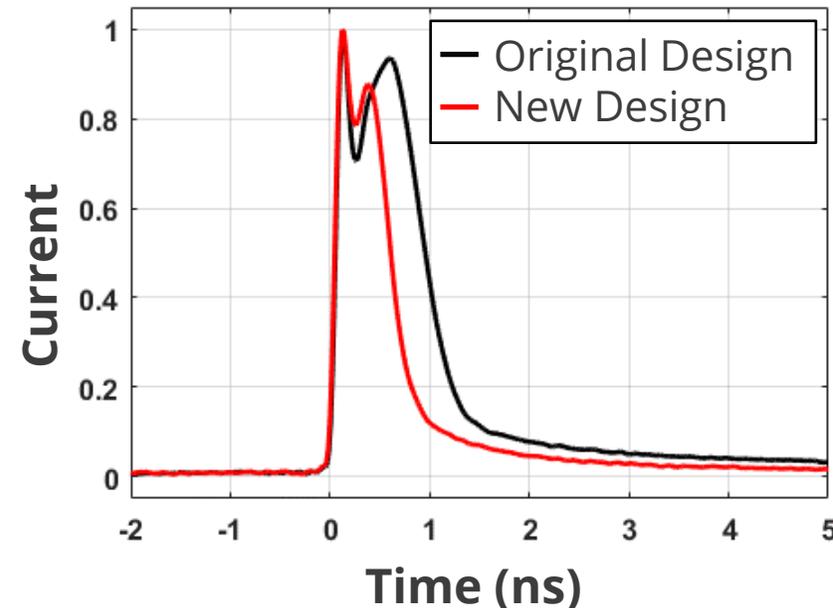
# Photodiode Temporal Response Is Now a Limiting Factor



- Overall detector response is convolution of ROIC gate and photodiode current
- With faster ROIC gates, PD current now uncovered as a limiting factor
- Thinner photodiode layer somewhat reduces charge collection time, but also reduces QE
- New PD pixel designs allow sub-ns collection time



Inferred Photodiode Signal from Gate Profile Deconvolution  
 Looker et al., *RSI* 92 053504 (2021)

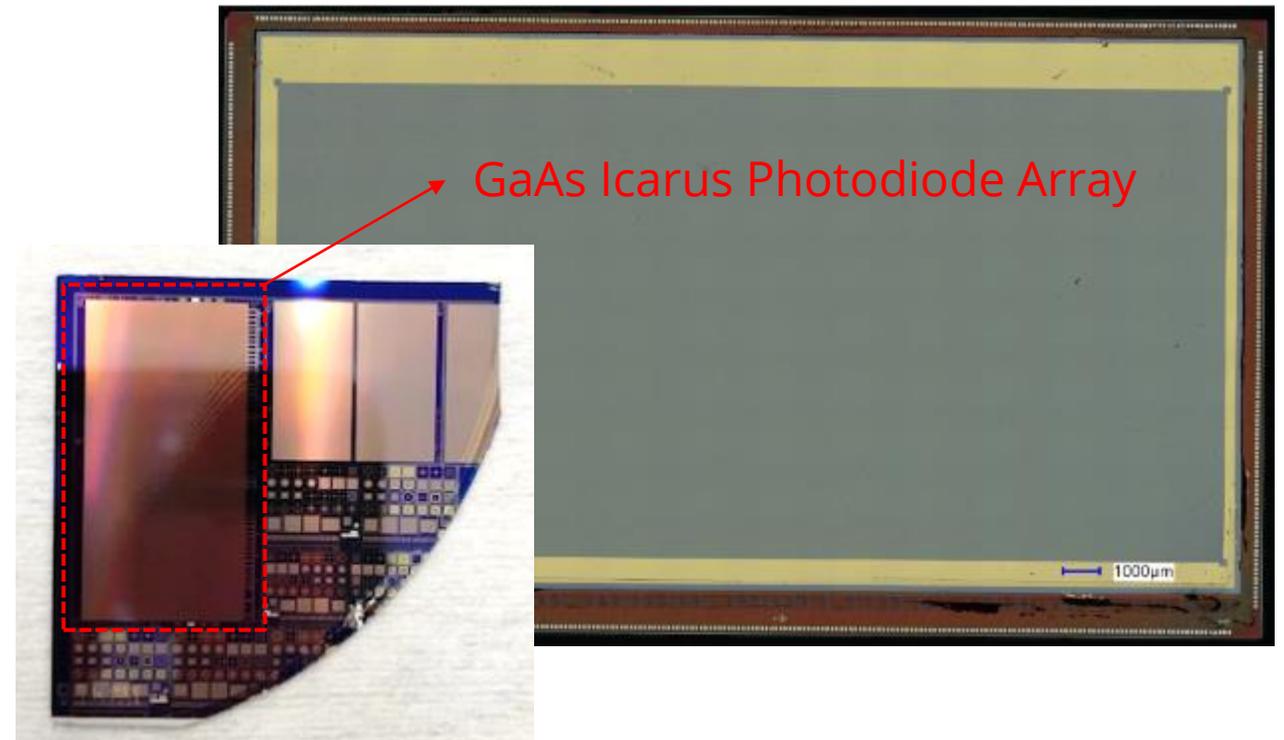
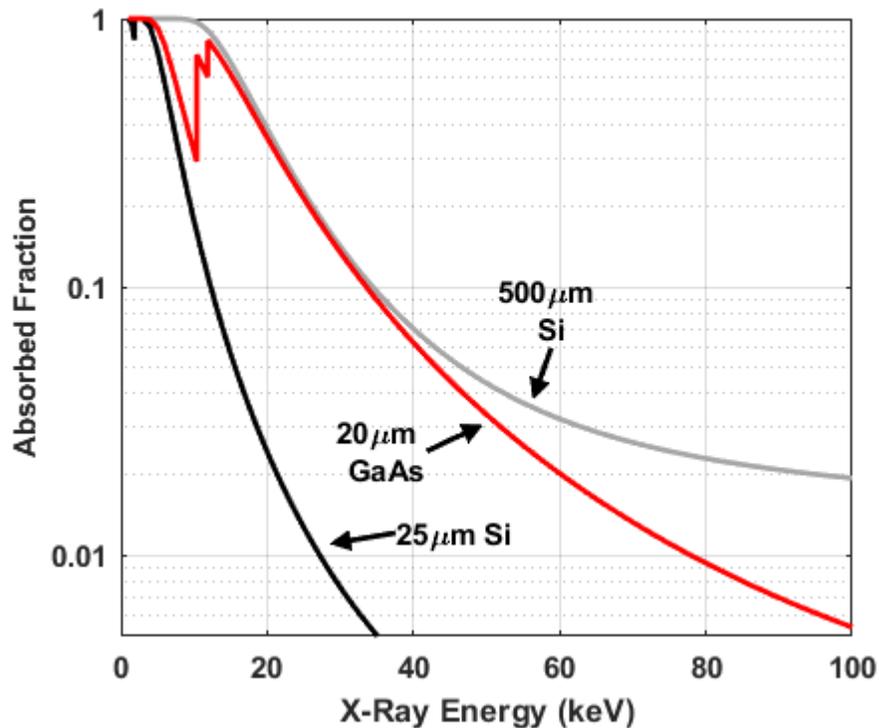


Measured Photocurrent from Test Devices

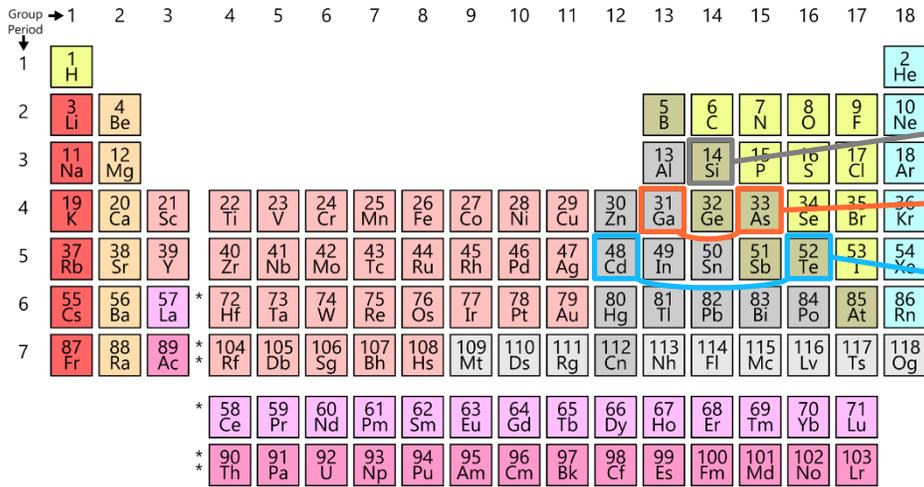
# A GaAs Photodiode Array Variant Is Under Development



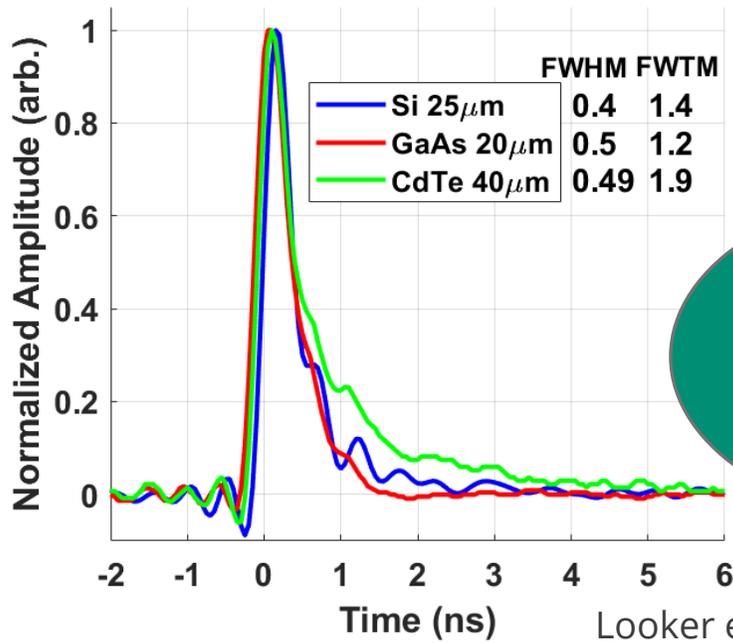
- Sensor replacement only: 25  $\mu\text{m}$  Si  $\rightarrow$  20  $\mu\text{m}$  GaAs
- Identical user experience and performance with enhanced hard X-ray sensitivity
- Fabrication process development underway



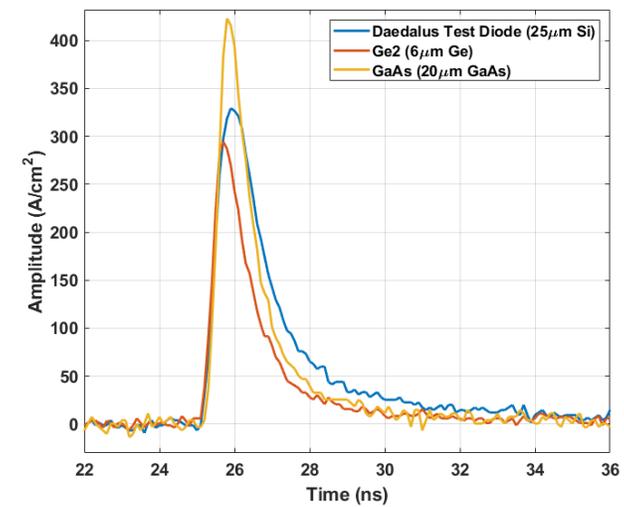
# Other detector materials show promise for hard x-ray detectors



Material Investigated	Notes
Si	Mature fabrication, low Z
GaAs	Demonstrated fast detectors
CdTe	Demonstrated fast detectors
Ge	APCVD grown shows promise
CdZnTe	Cannot obtain small detectors
GaN	Background doping too high
PbSe	Thick layers difficult

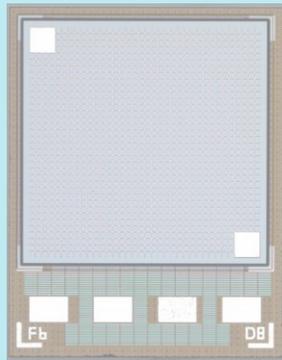
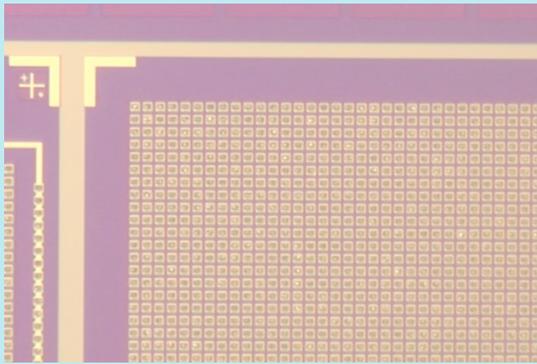


Detector pulse shapes obtained with Advanced Photon Source white beam



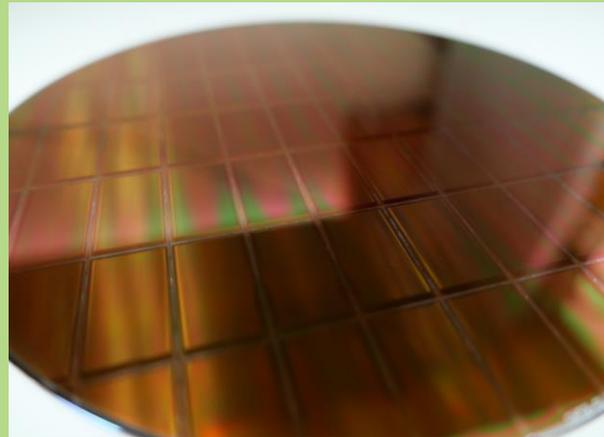
## Sensor development

- Faster charge collection
- Higher atomic number



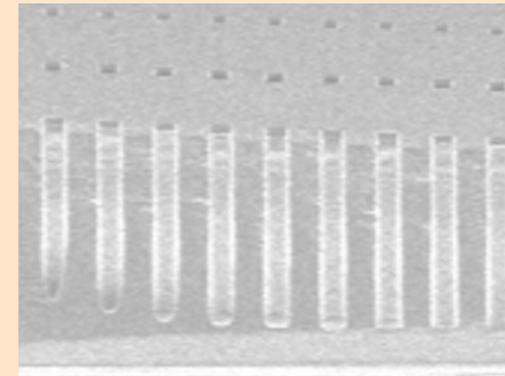
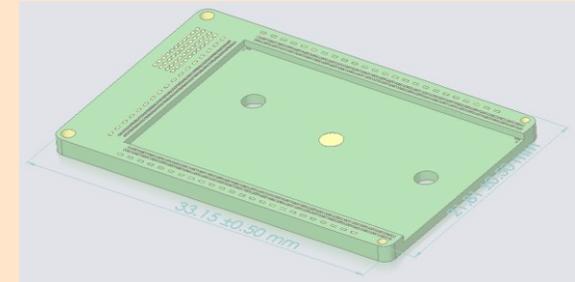
## ROIC development

- Faster gate times
- Increased number of frames
- Smaller nodes
- Commercial foundries

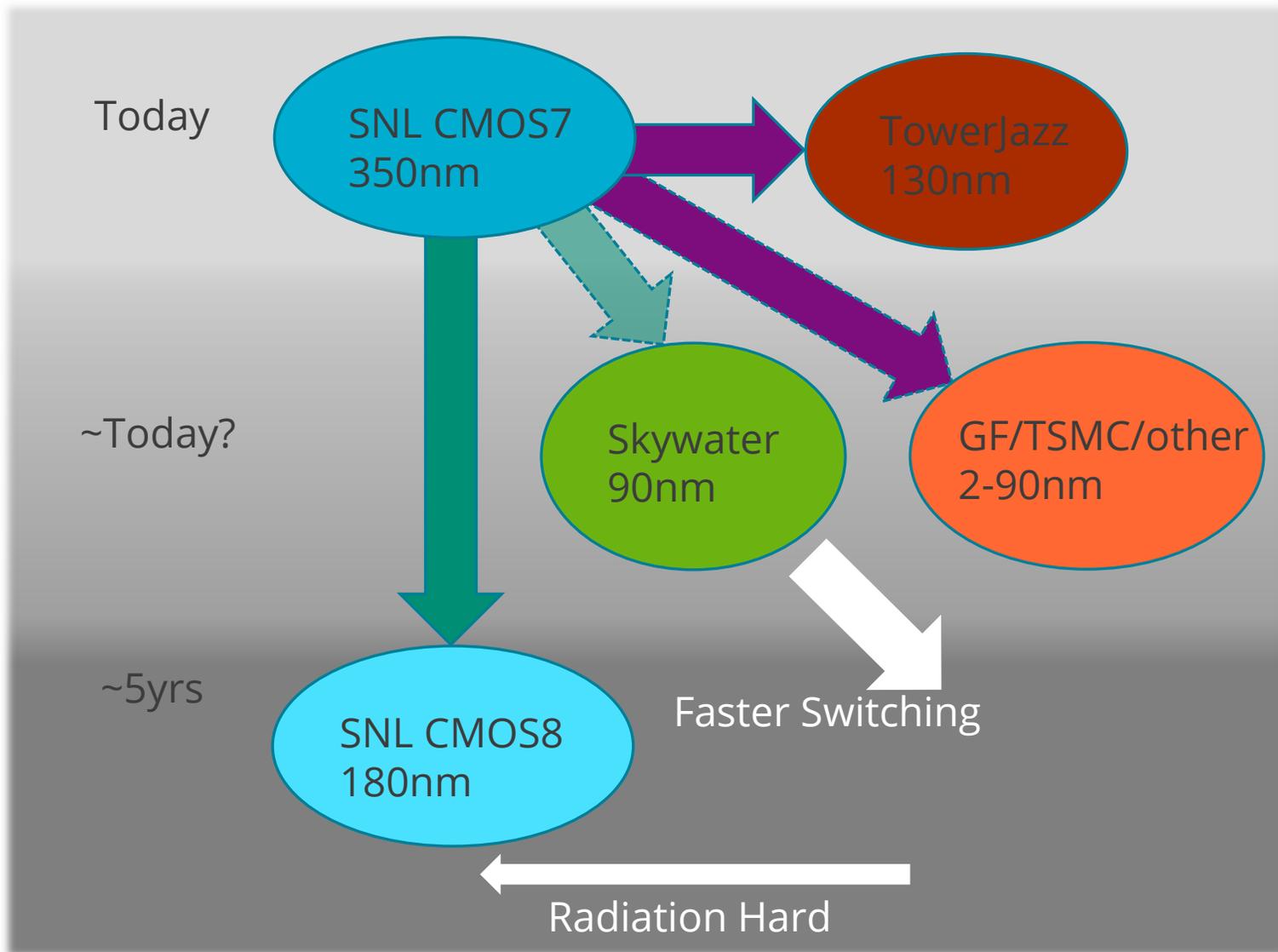


## Package development

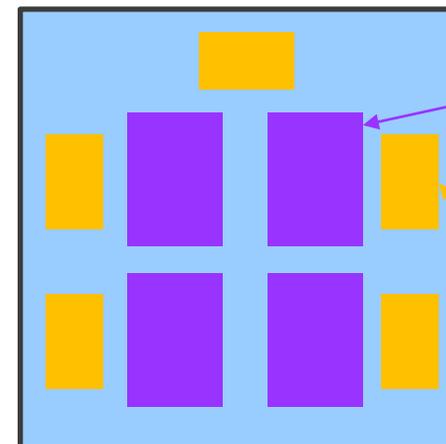
- Improved PCB Design
- Through Si Vias
- Thermal Management



# Smaller Nodes May Enable More Frames with Faster Gate Time



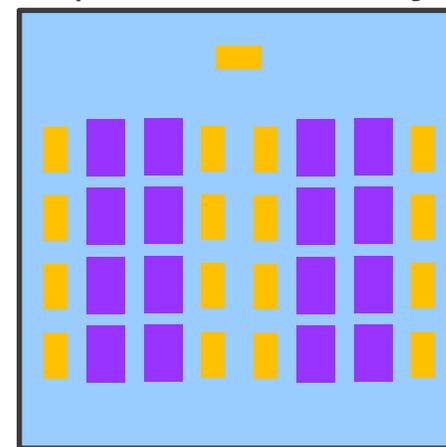
Existing Pixel Layout



Analog  
Storage

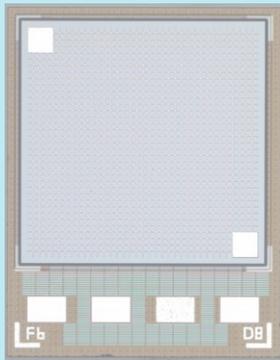
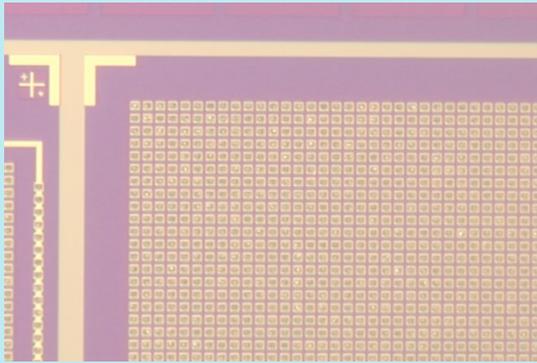
Transistors

Prospective Pixel Layout



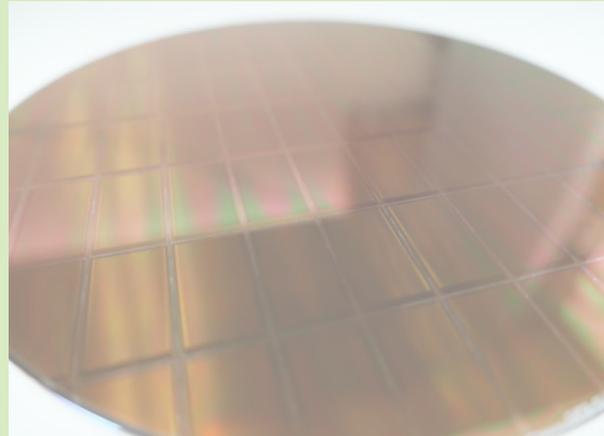
## Sensor development

- Faster charge collection
- Higher atomic number



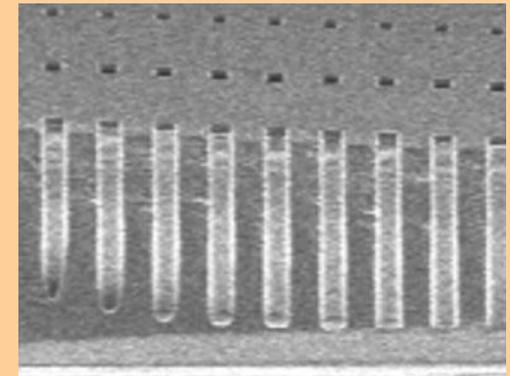
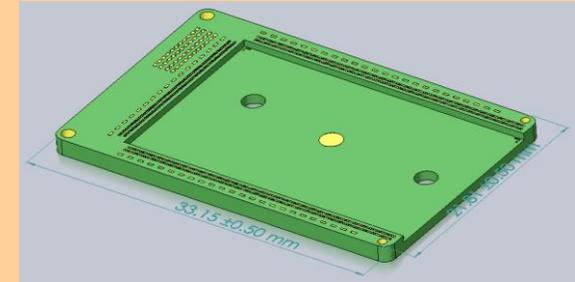
## ROIC development

- Faster gate times
- Increased number of frames
- Smaller nodes
- Commercial foundries



## Package development

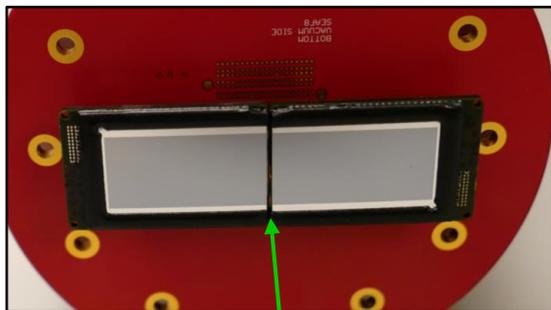
- Improved PCB Design
- Through Si Vias
- Thermal Management



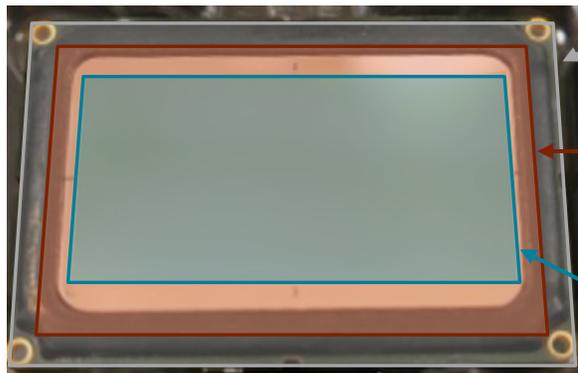
# Packaging Improvements Increase Total Image Size and Aid Thermal Stability



## Abutable Modules Multiply Image Area



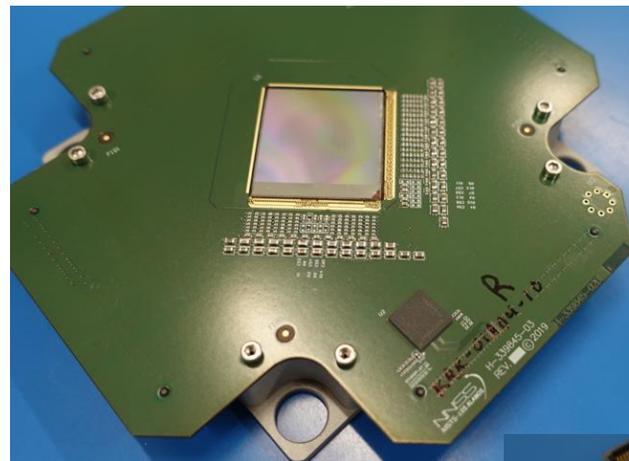
1.25mm Gap  
Combined 12.8mm x 51.2mm Area



Package Outline  
Die Outline  
Active Area

Eliminate bond pad periphery with TSVs

## Packages with thermal management



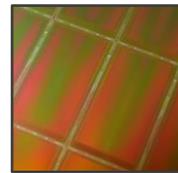
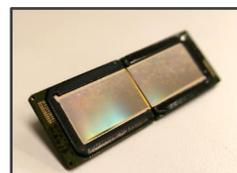
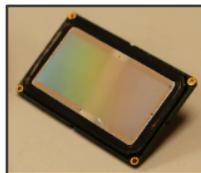
- Lower read noise
- Better timing stability



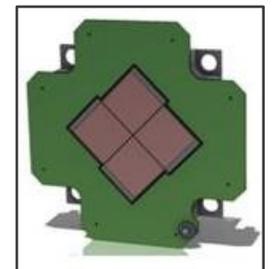
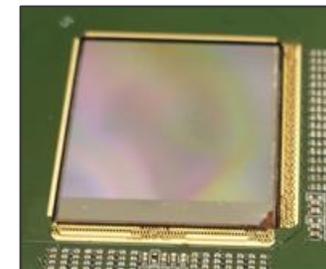
# Summary and Questions



	Deployed	Prototype	In Production
	Icarus V1/V2	Daedalus V1/V2	Tantalus
Year	FY16-18	FY18-23	FY24
Min. Integration time	~1.5 ns	~1.0 ns	~0.5 ns
Frames	4 (full resolution) 8 (L/R interlaced)	3 (full resolution) 6+ (Row/L/R interlaced)	4 (full resolution) 16+ (Row/quad. interlaced)
Tiling Option	No	One Side	No
CMOS Process	350 nm (SNL)	350 nm (SNL)	130 nm (Tower Jazz)
Pixels	512 × 1024	512 × 1024	512 × 1024
Pixel Size	25 μm × 25 μm	25 μm × 25 μm	25 μm × 25 μm
Capacitor Full Well	0.7 million e <sup>-</sup>	1.5 million e <sup>-</sup>	0.5 million e <sup>-</sup>



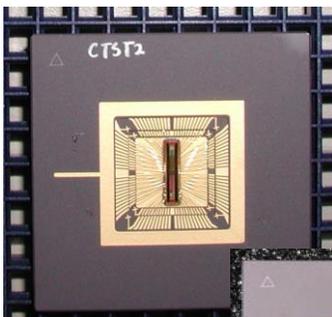
	Prototype	In Production
	Kraken V1	Kraken V2
Min. Integration Time	50 ns	50 ns
Min. Interframe Time	50 ns	50 ns
Effective Dynamic Range	>11 bits (68 dB)	>11 bits (68 dB)
Read Noise	158 e <sup>-</sup>	< 100 e <sup>-</sup>
Frames	4 (8 without CDS)	8
Pixels	800 × 800 (2 side abutable)	800 × 800 (2 side abutable)
Pixel Pitch	30 μm	30 μm
Chip Size	24 x 24 mm	24 x 24 mm
Capacitor Full Well	0.4 million e <sup>-</sup>	0.4 million e <sup>-</sup>





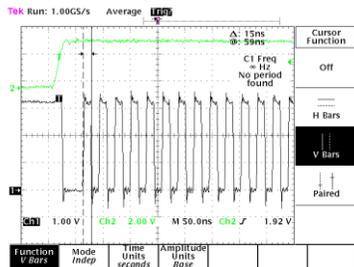
# hCMOS Detectors of Today Are the Result of Significant Development

2011

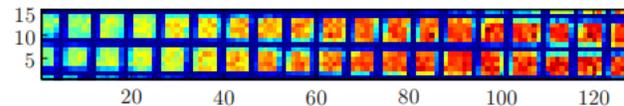


Phoenix

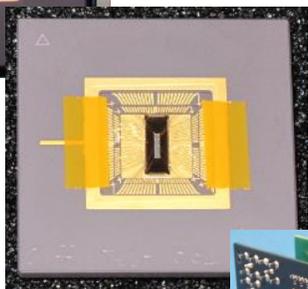
Demonstration of fast onboard timing



X-ray images of wire grid



2012

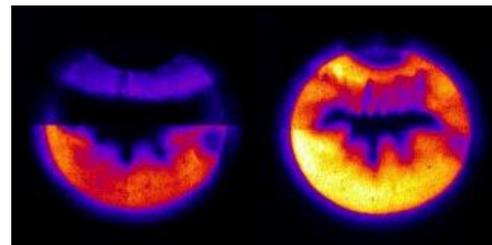


Griffin

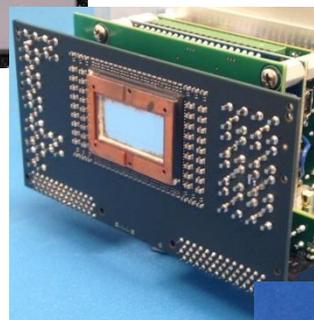
Demonstration of x-ray imaging on 128x15 array



GLEH on NIF



2014



Furi

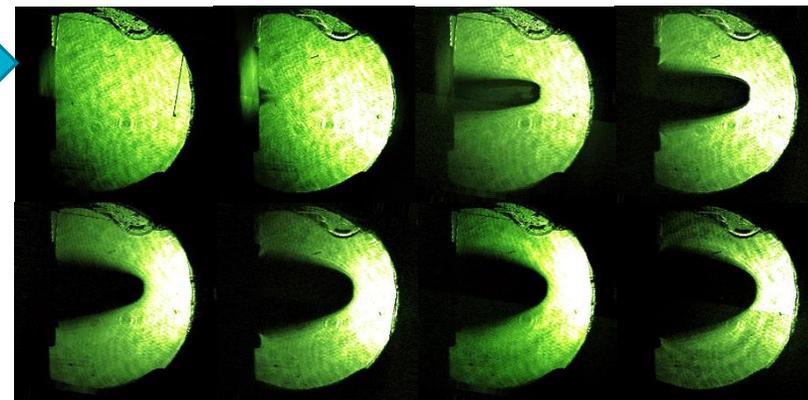
First full-scale ultrafast x-ray imager



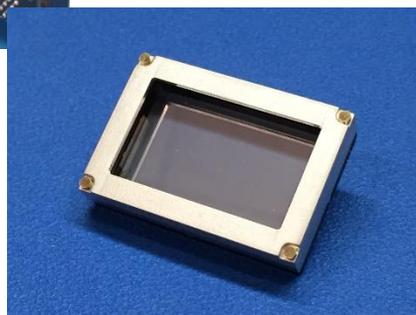
Hippogriff

More frames in a smaller package

Shadowgraphy of Gas Cell



2015



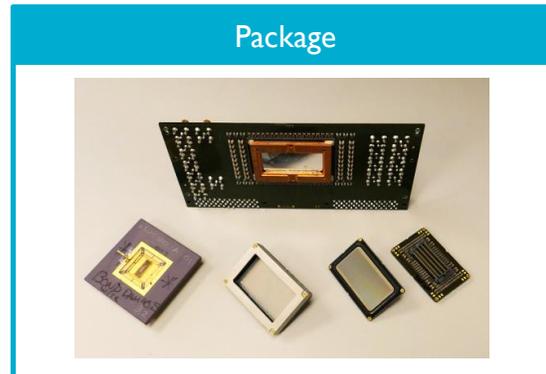
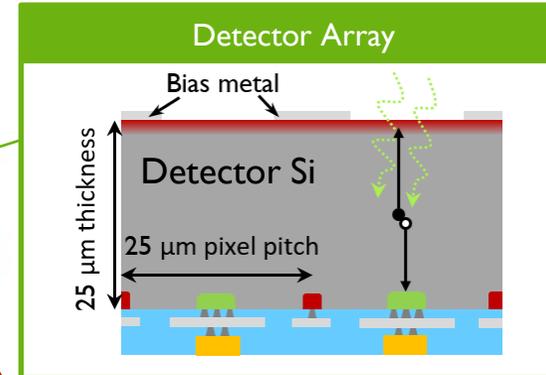
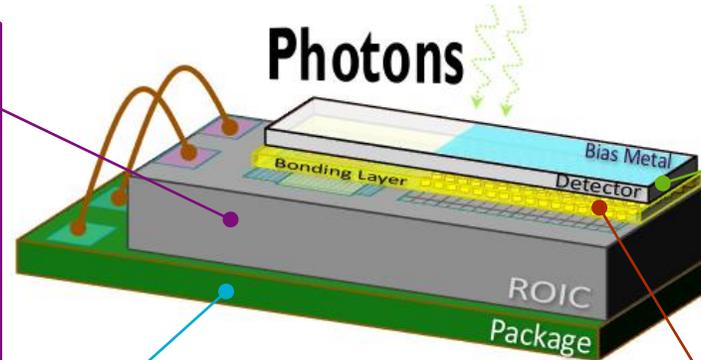
# Many Parts and Processes Come Together to Form a UXI Camera



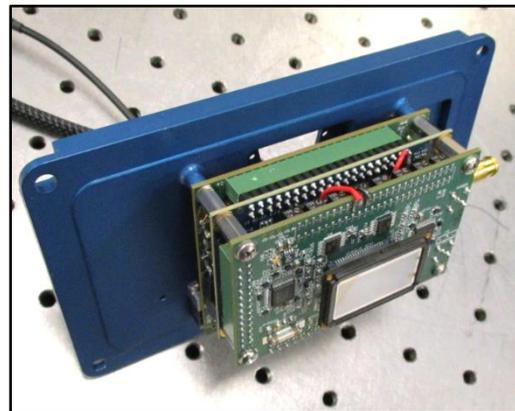
**Readout Integrated Circuit (ROIC)**

Furi Hippogriff Icarus Daedalus

- Fabricated in SNL's 6" 350nm CMOS
- 1-2ns min shutter, 2-8 frames
- 1024x512 array of 25 $\mu$ m x 25 $\mu$ m pixels
- Adjustable shutter timing



**Hybrid CMOS  
Sensor**



**Integration**

**Direct Bond Interconnect (DBI)**

- External supplier
- Wafer-to-wafer bond

**Indium bump**

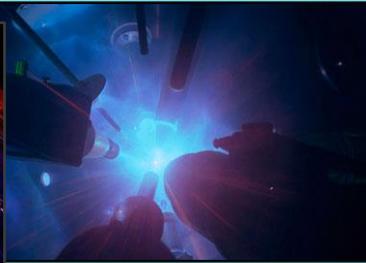
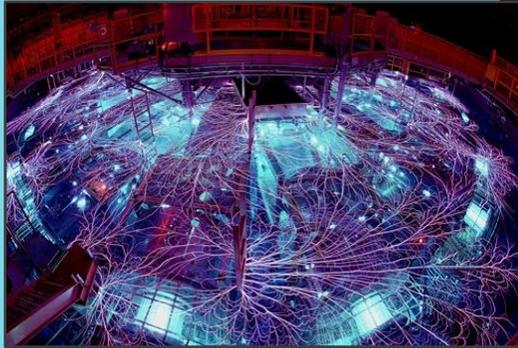
- Processing at Sandia
- Die-level processing

**UXI Camera System Development  
for Application-Specific Needs**

# Sandia's Hybrid CMOS Detectors were Developed for Inertial Confinement Fusion and High Energy Density Physics Applications

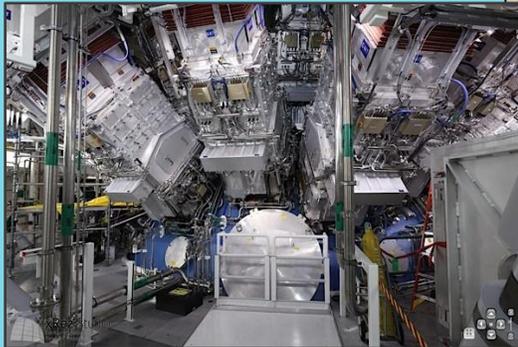


## National ICF Facilities



OMEGA LLE

Sandia Z Machine



CEA LMJ

Livermore NIF

- High Intensity (~MJ x-rays,  $10^{17}$  neutrons in ~ns)
- Low Shot Rate (<5 shots/day)

## Key Detector Attributes

- Radiation Hard
- EMI Resistant
- Selective Sensitivity
- Temporal Resolution
- Shock and Debris Resistance

## Tools of the Trade

- Photodiodes/PCDs/X-ray Diodes
- Organic Scintillator + PMT
- X-ray Film/Image Plate
- Microchannel Plate
- Streak Camera

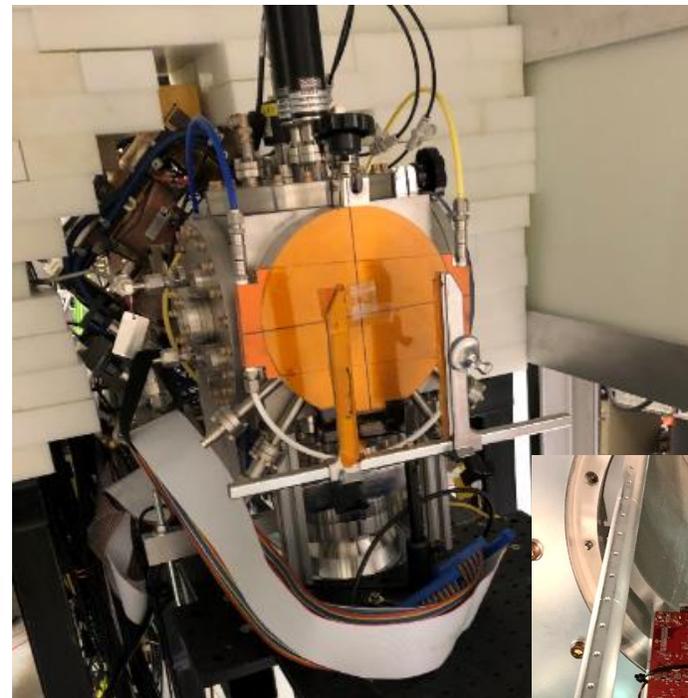


# hCMOS Detectors are Created With a Radiation Hardened Process

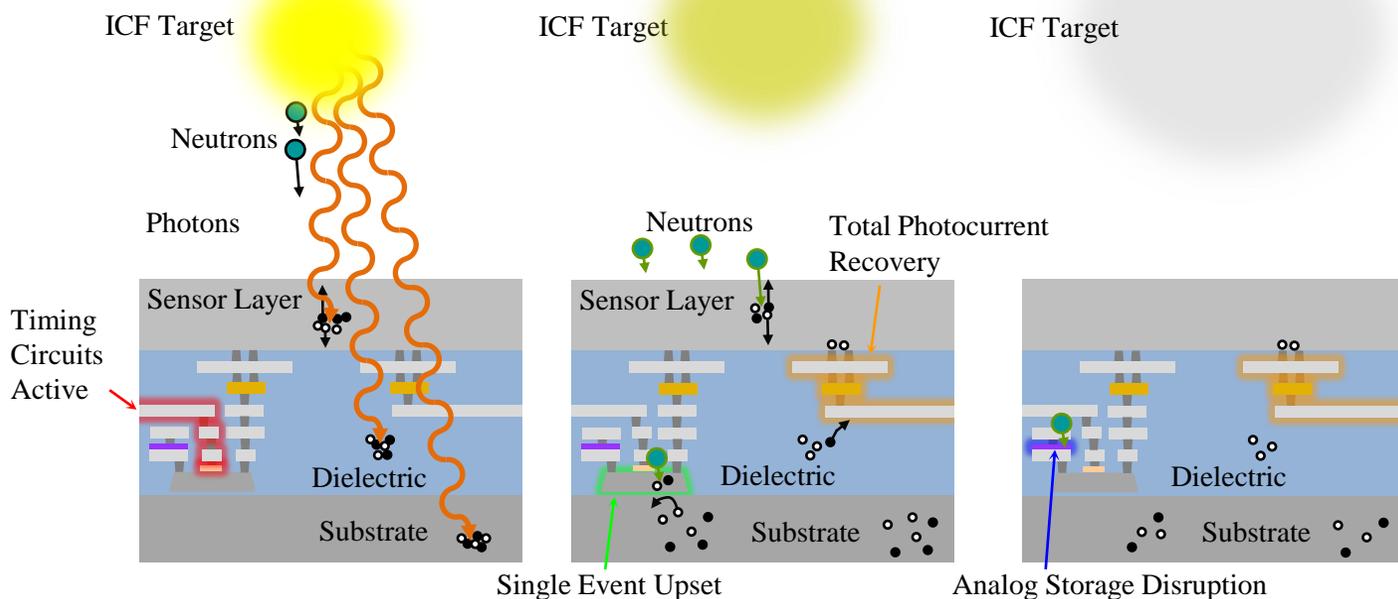


- All detectors in the family are fabricated in Sandia's rad hard CMOS7 350 nm process
- ASIC design minimizes active circuitry during irradiation
- Need to quantify total system tolerance to total neutron dose and single event upsets
- Sandia's Ion Beam Laboratory Irradiation station for NIF-relevant dose of D-D or D-T neutrons
- NIF neutron test well

D-D/D-T Neutron Irradiation Station



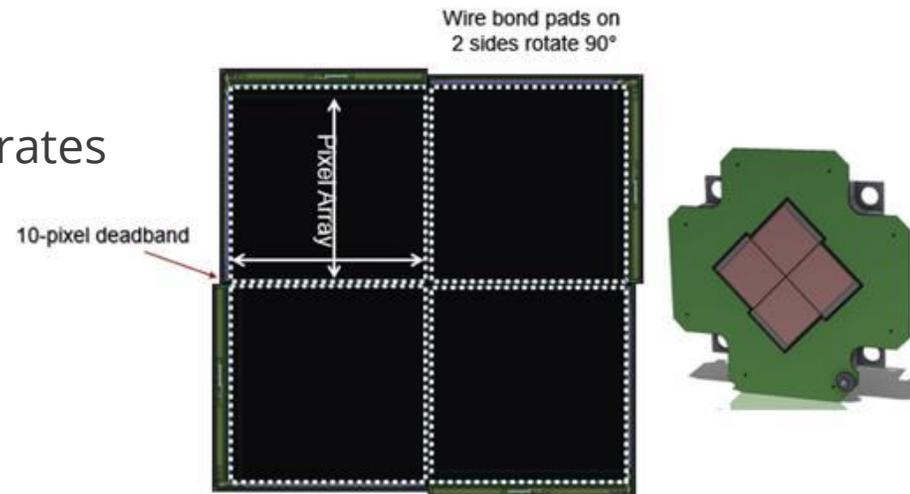
NIF Neutron Test Well



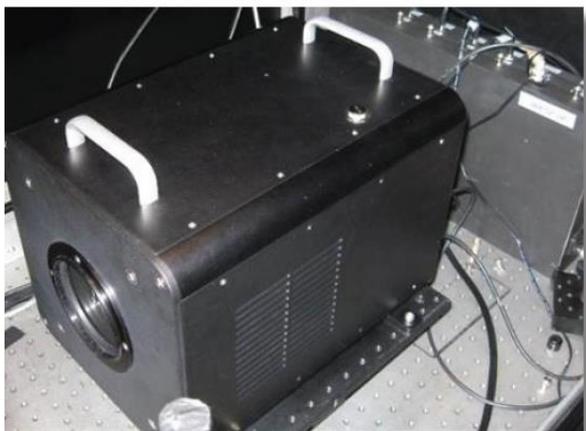
# The Related Instrument Line Kraken is Targeted to Multi-Frame Radiography

- Longer integration times
- Lower read noise
- More frames

Kraken V2 incorporates 2-side abutability



## Kraken V1



Item	Specification
Minimum integration time	50 ns
Minimum interframe time	50 ns
Array size	800 × 800 pixels with 2-side abutment
Pixel size	30 μm
Read noise	157 e <sup>-</sup>
Full well	490,000 e <sup>-</sup>
Dynamic range	3,130
Sensitivity	5.71 × 10 <sup>12</sup> e <sup>-</sup> /(J/cm <sup>2</sup> )

8-frame Radiograph Set of Laser-Irradiated Silica Beads

